

DESY Seminar
Hamburg, April 29, 2008

The CDF Silicon Detector: Design – Operations – Studies

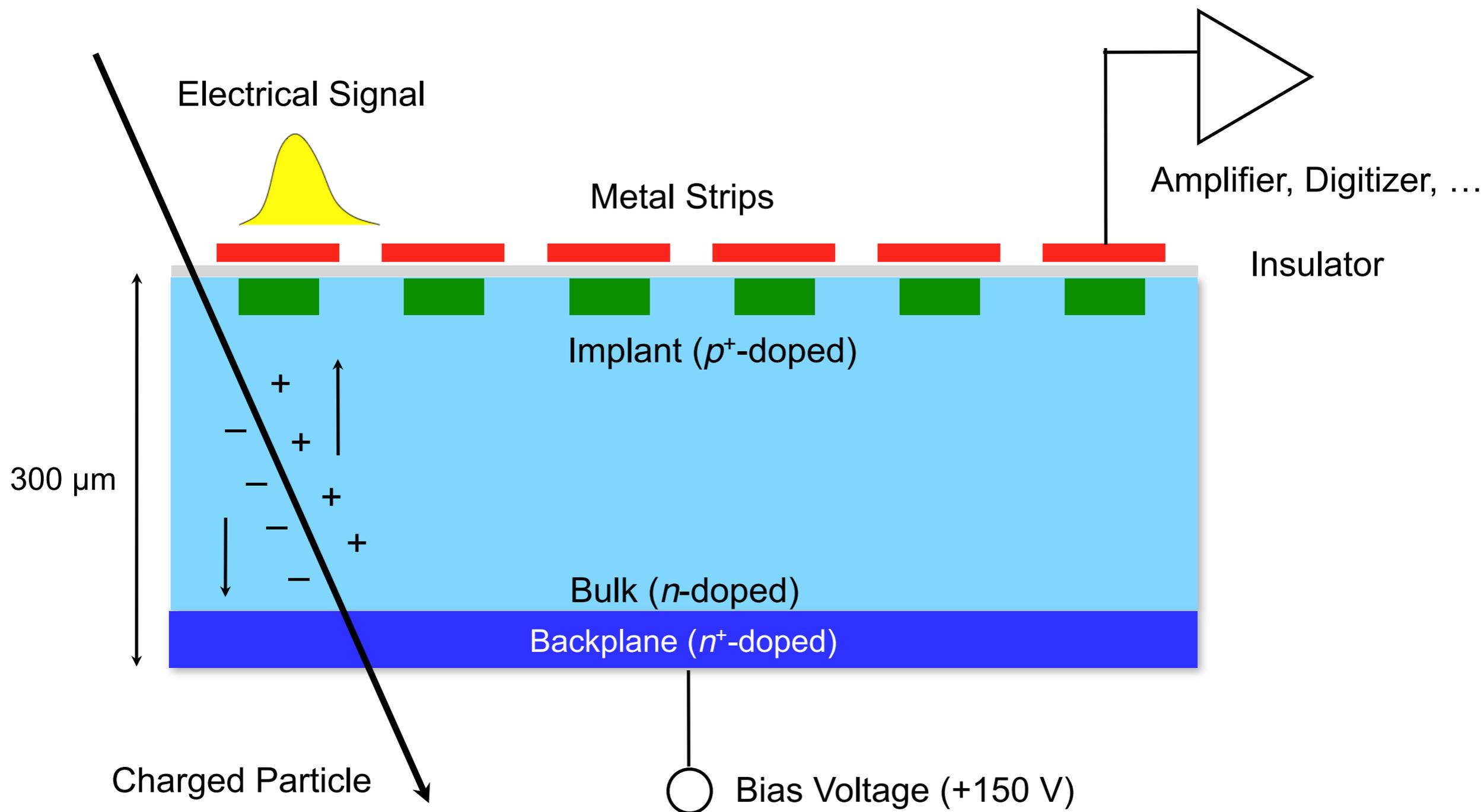


Ulrich Husemann
Deutsches Elektronen-Synchrotron



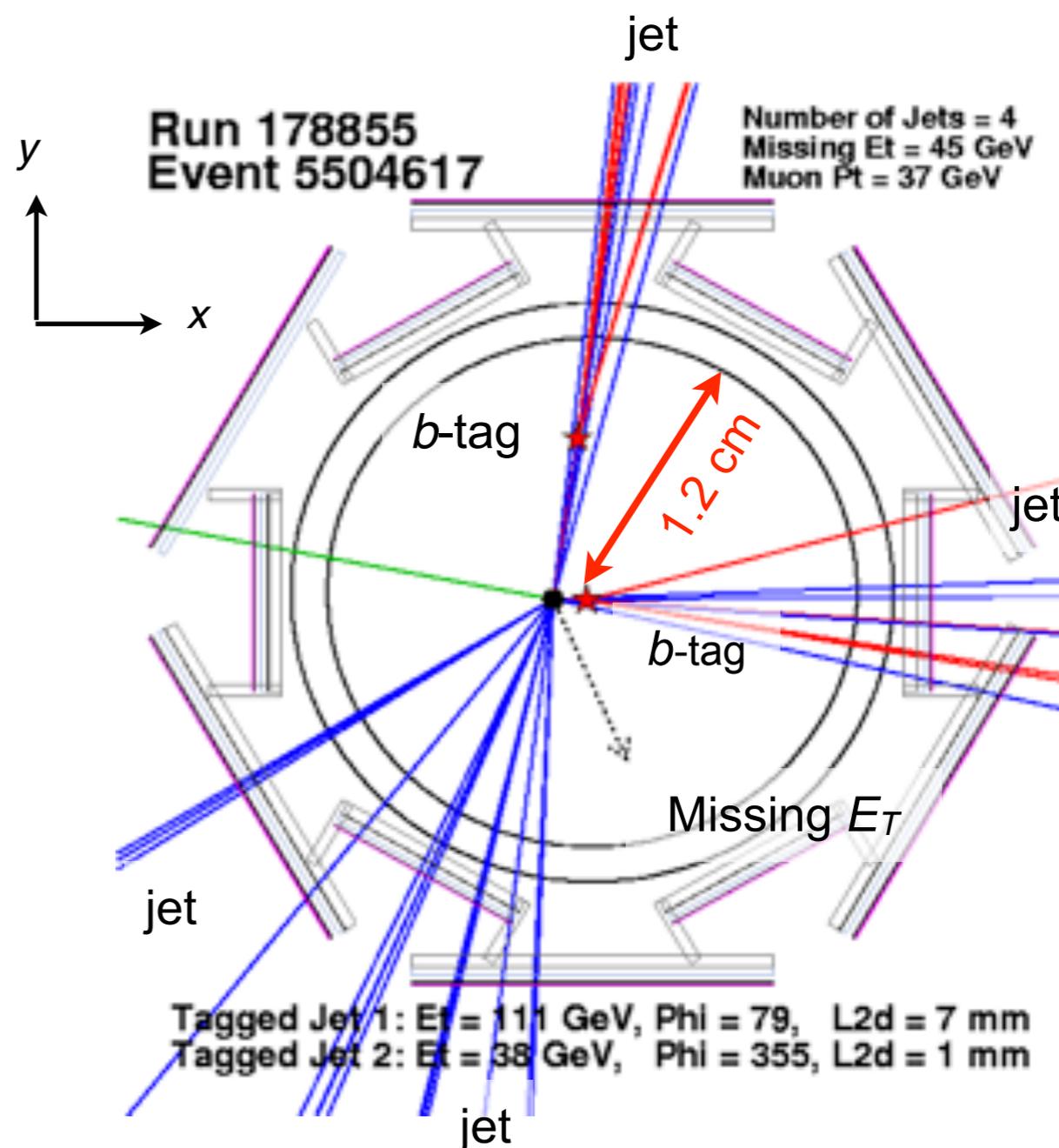




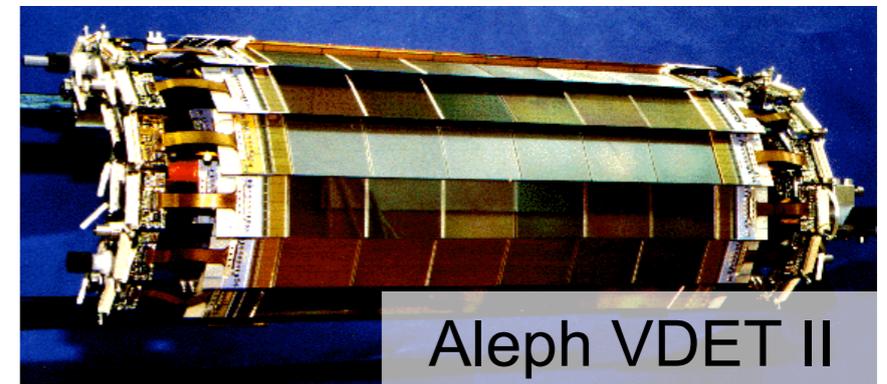


- Precision tracking
 - **Momentum** measurement = measurement of track **curvature**: dominated by larger tracking device, e.g. drift chamber
 - **Impact parameter** = closest distance between track helix and beam axis: need **precision tracking point close to primary interaction**
- *B*-tagging
 - Decays of long-lived *B* mesons ($c\tau \approx 500 \mu\text{m}$) lead to **displaced vertices**
 - Identification of *b*-jets: displaced secondary vertex (cut on **decay length significance**)

Double-Tag Event in Layer 00 of CDF Silicon Detector

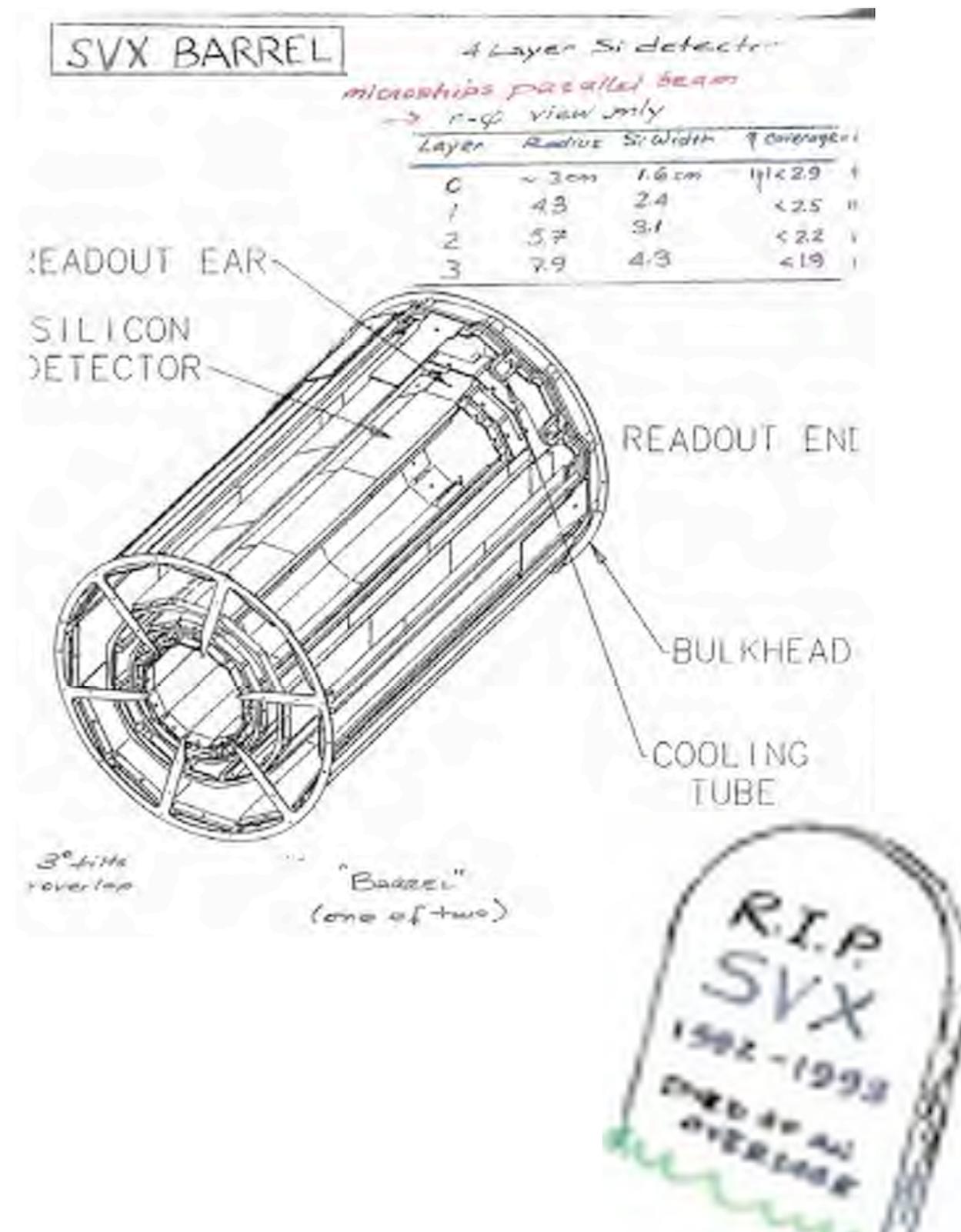


- Today: Silicon detectors **standard tool** for precision tracking and vertexing (esp. secondary vertex heavy flavor tagging)
- First particle physics application of silicon detectors: high-rate **fixed target experiments for charm physics** (esp. *D* meson lifetimes)
 - CERN NA11 (ACCMOR Collaboration): ~1983
 - Fermilab E691 (Tagged Photon Spectrometer): ~1985
- Silicon microstrip vertex trackers at **electron-positron colliders** (1990s)
 - All LEP detectors, Mark-II at SLC
 - *B* factories
- First application in a **hadron collider** (CERN Sp \bar{p} S): UA2 (1987)
 - Single cylinder of silicon pads ($8.7 \times 40 \text{ mm}^2$): 60 cm long, 14.7 cm radius, 1 m² of sensor surface, mounted directly on the beam pipe



Aleph VDET II

- First ideas in 1983
- Concept of silicon detectors at hadron colliders **controversial** within CDF (e.g.: occupancy of inner layers too high?)
- First design: **SVX** (operated 1992–1993)
 - 2 barrels with 4 layers each, 51.1 cm long, radii: 3–8 cm
 - **Single sided** sensors (60 μm pitch), **DC-coupled** readout
 - Short lifetime mainly due to **radiation damage** to the readout chip: increased occupancy, reduced efficiency





But Nevertheless...



PHYSICAL REVIEW D

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1 SEPTEMBER 1994

ARTICLES

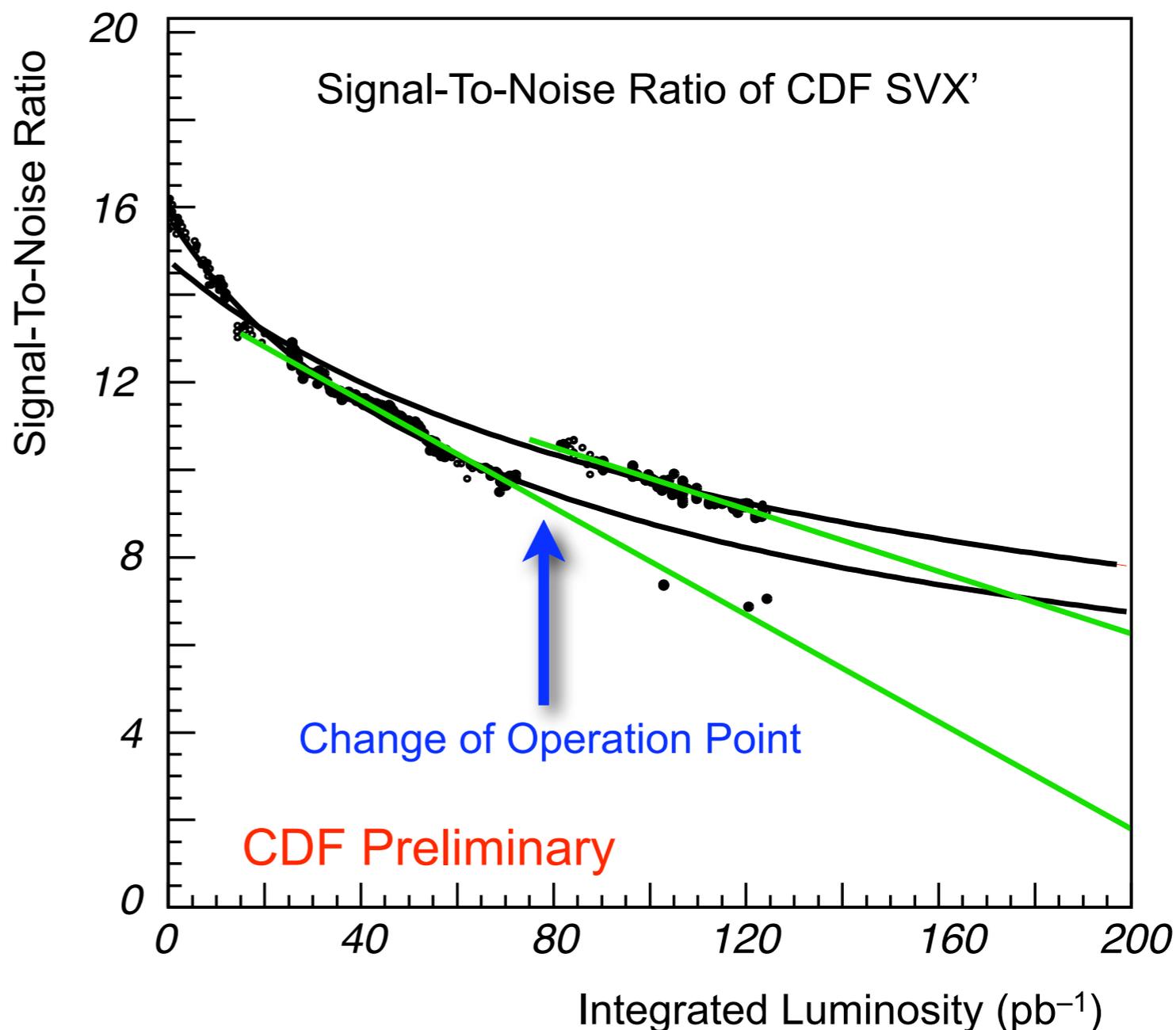
Evidence for top quark production in $\bar{p}p$ collisions at $\sqrt{s} = 1.8$ TeV

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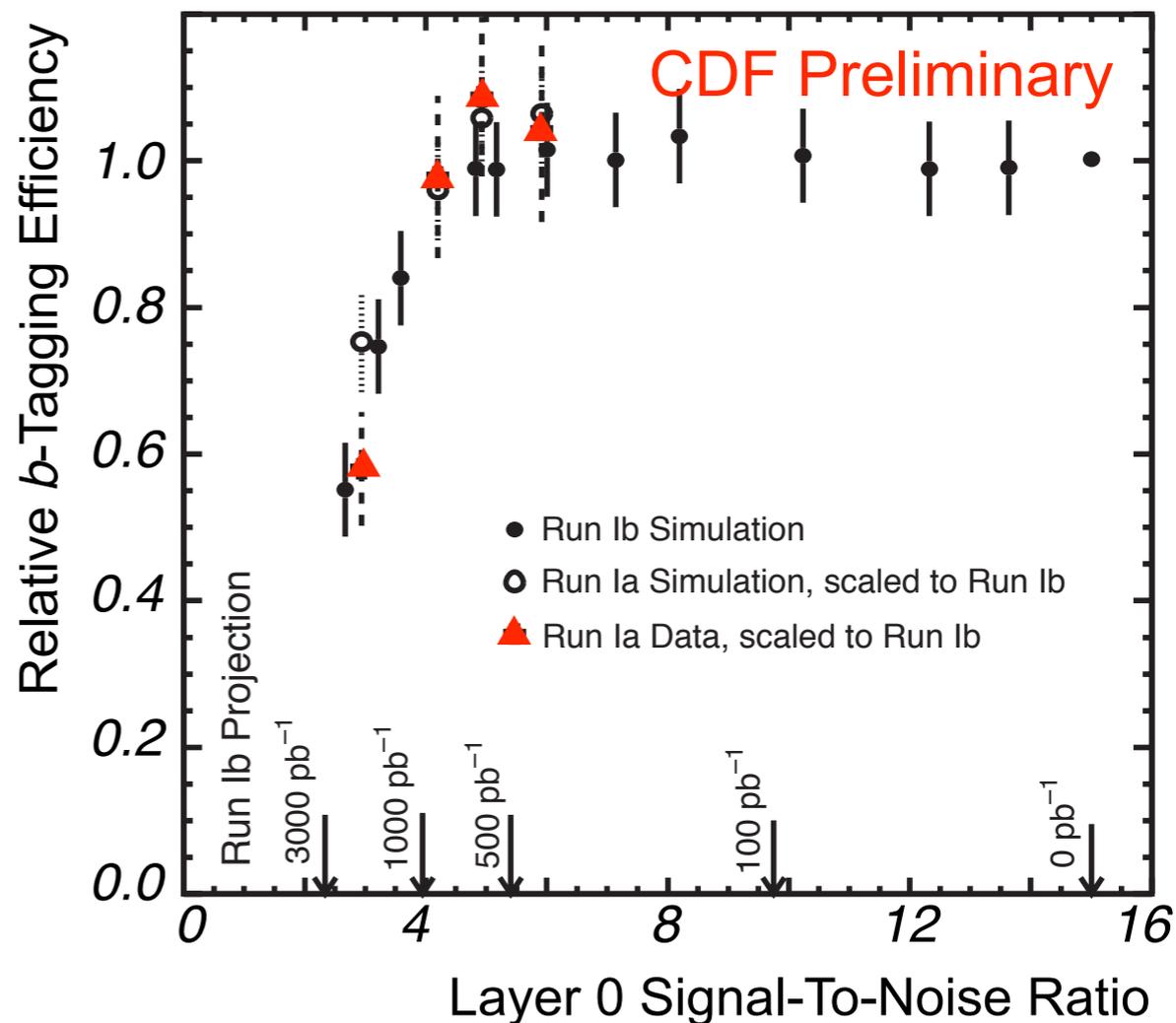


...The Top!

- Second attempt: **SVX'** (operated 1993–1996)
- Mechanical design similar to SVX, slightly smaller inner radius (2.8 cm)
- **Radiation hard** readout chip
- **AC-coupled** readout with FOXFET (Field Oxide FET) biasing
- Signal-to-noise ratio (SNR) decreases faster than expected (attributed to FOXFET biasing)
- Reduction of SNR partly **compensated by changes in detector operation** (integration time, temperature, bias voltage)



- Secondary vertex ***b*-tagging**:
 - Efficiency drops quickly for **SNR smaller than approx. 3**
 - But: top quark discovery with data taken with SNR of 6 \rightarrow 3
- Detector resolution:
 - **Great impact parameter resolution** (SVX' only: 35 μm , 46 μm including beam spot)
 - **Poor p_T resolution**: short lever arm, radii: 3–8 cm \rightarrow **additional layer** at larger radius (~ 20 cm)
- Some limitations can be overcome by **clever software** (and people)

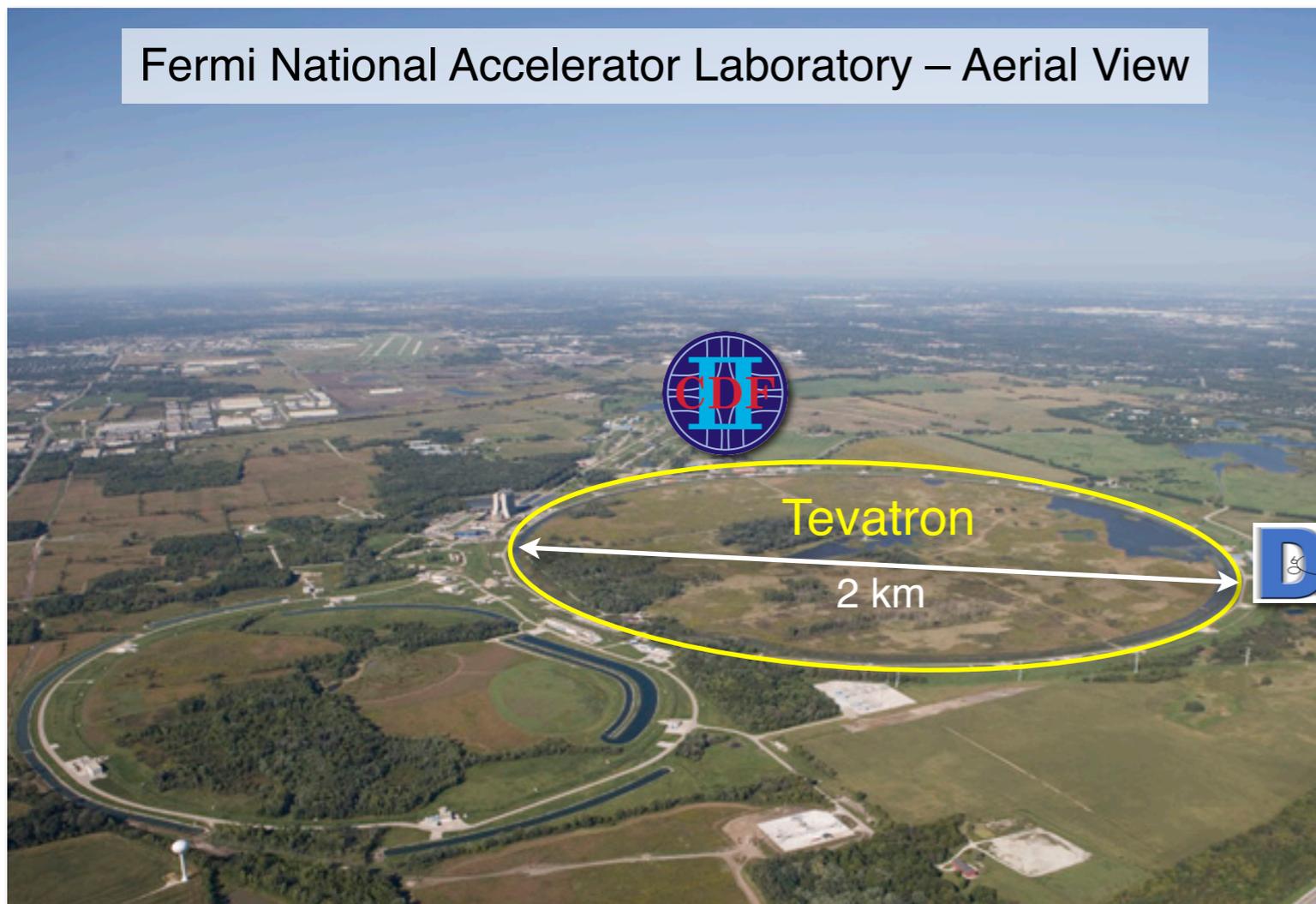


For more details on the history of Silicon detectors in CDF (and CMS):

J. Incandela, *Life on the Critical Path*

(talk given at the 6th International "Hiroshima" Symposium, Carmel, CA, September 11–15, 2006)

Fermi National Accelerator Laboratory – Aerial View



[Fermilab Visual Media Service]

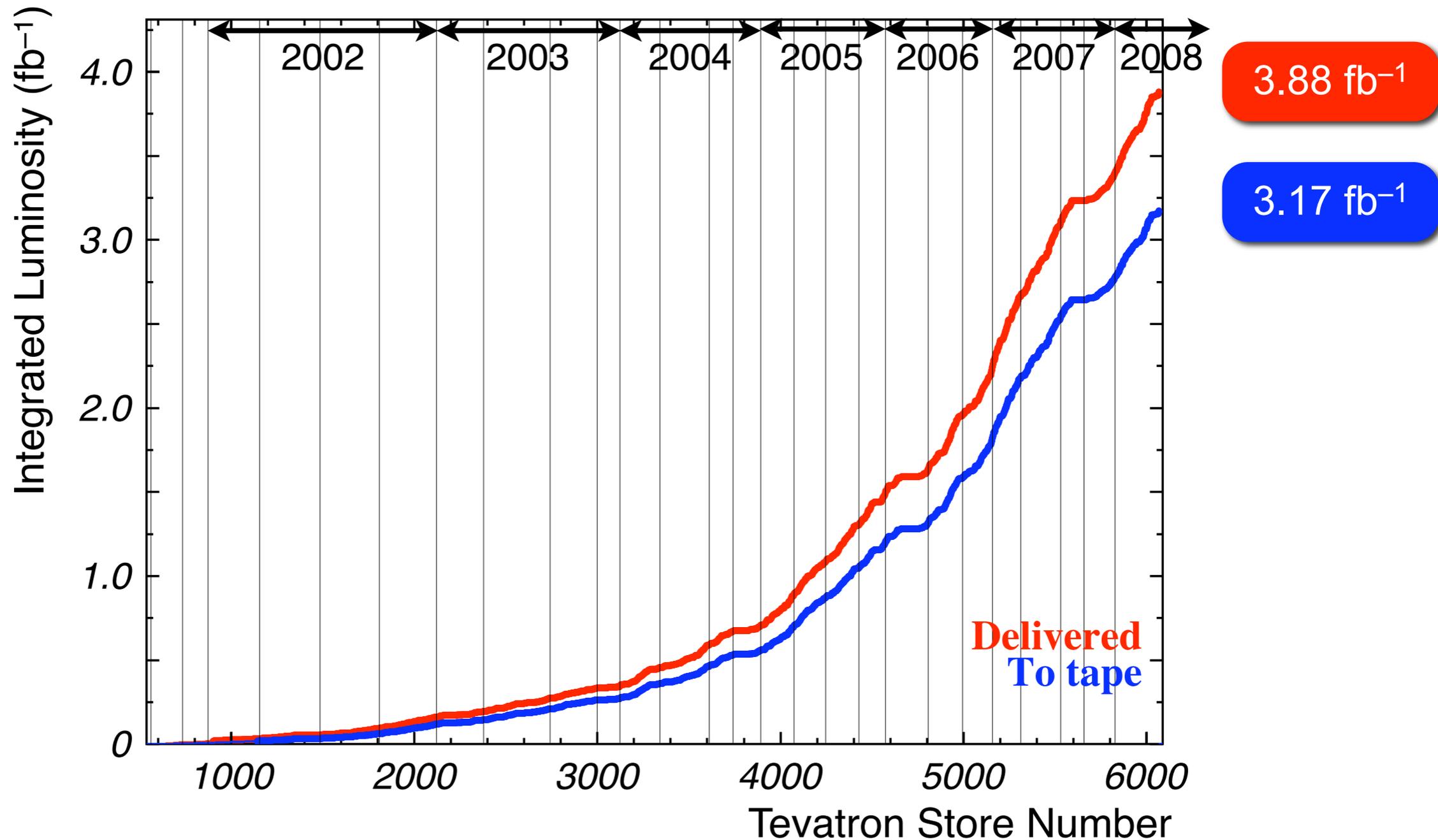
- Proton-antiproton collider:
 $\sqrt{s} = 1.96 \text{ TeV}$
- 36×36 bunches, collisions every 396 ns
- Record instantaneous peak luminosity:
 $316 \mu\text{b}^{-1} \text{ s}^{-1}$
($1 \mu\text{b}^{-1} \text{ s}^{-1} = 10^{30} \text{ cm}^{-2} \text{ s}^{-1}$)
- Luminosity goal:
 $5.5\text{--}6.5 \text{ fb}^{-1}$ of integrated luminosity by 2009, running in 2010 currently under discussion
- Two multi-purpose detectors: CDF and DØ

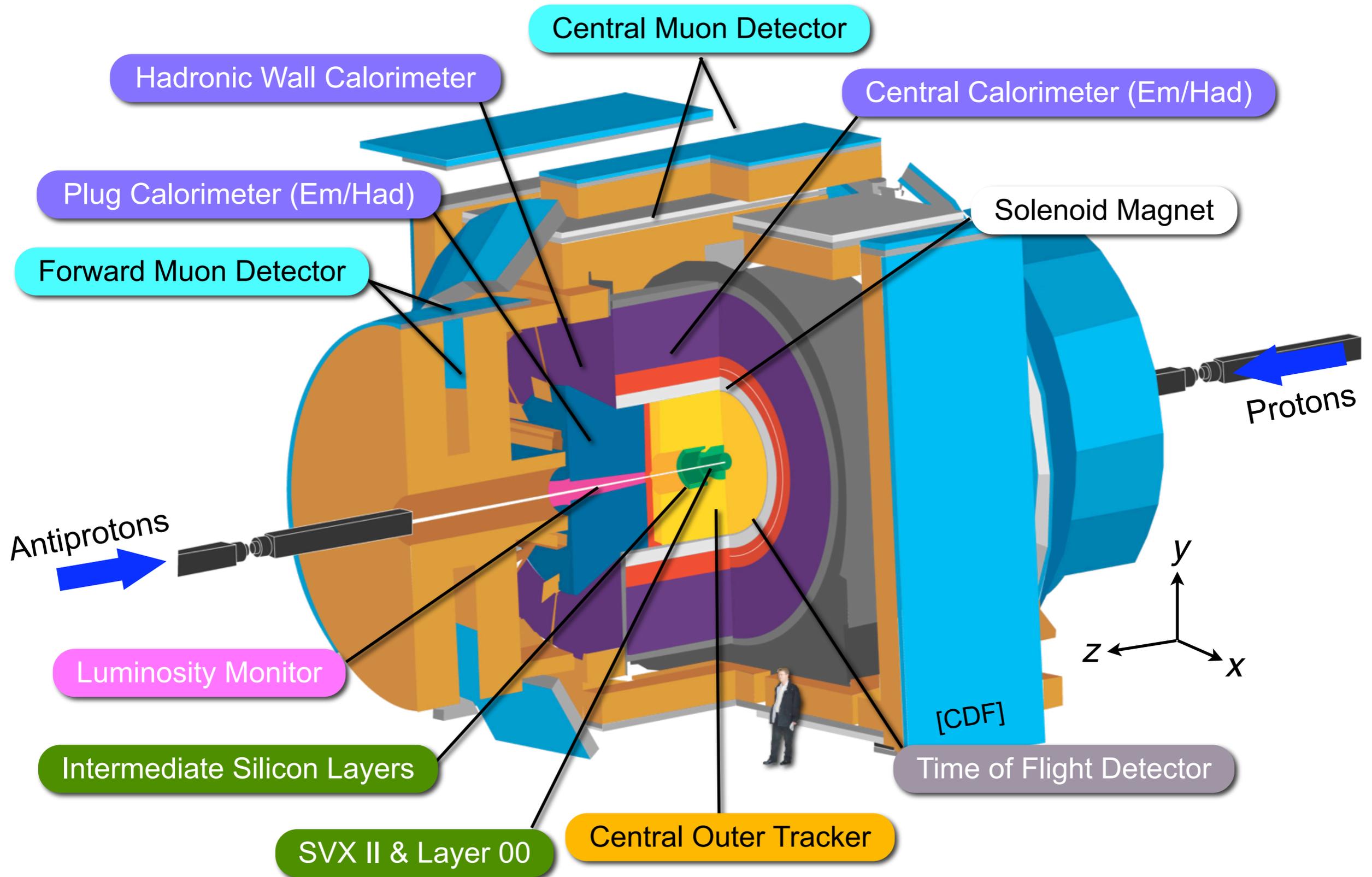


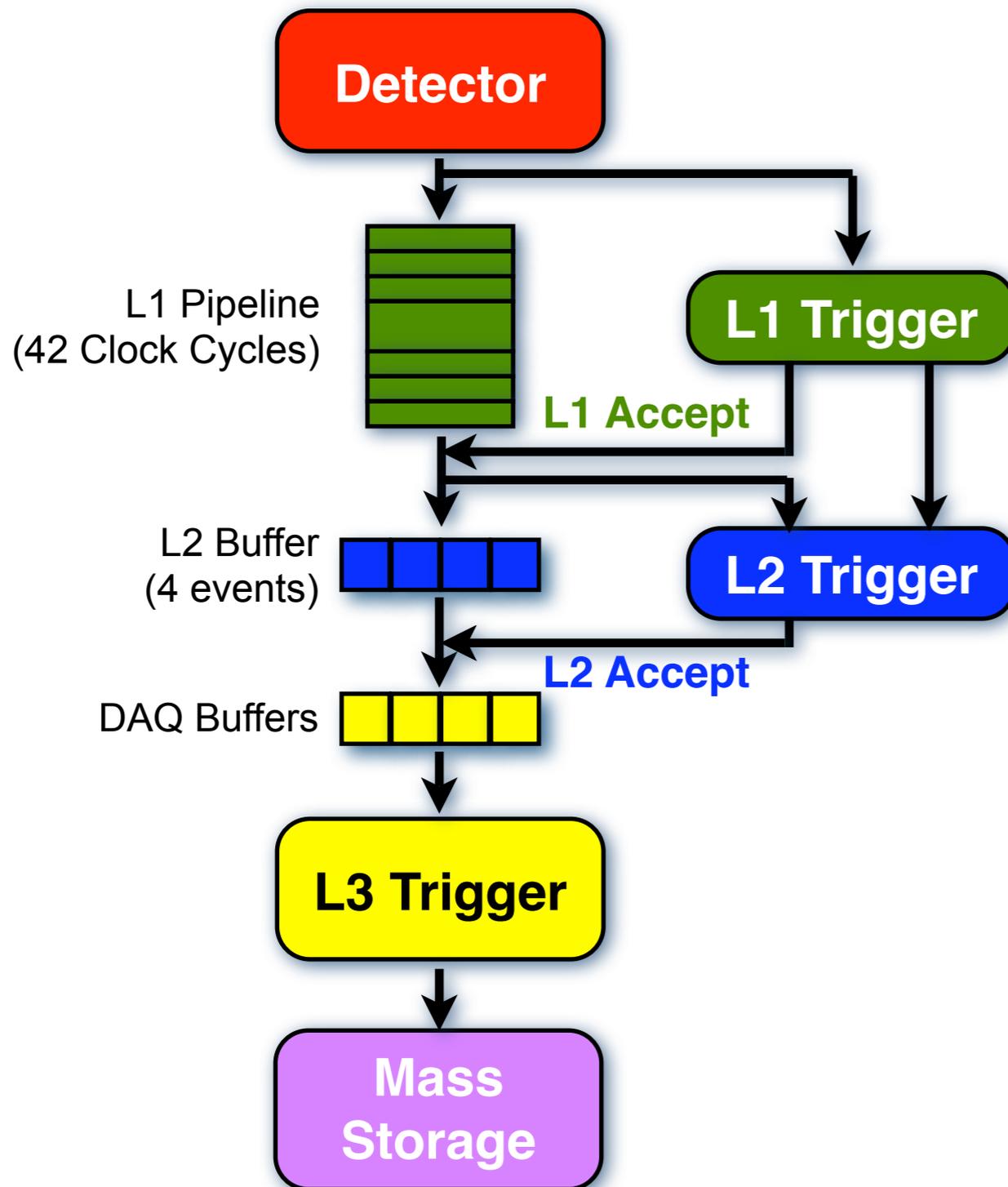
Tevatron Performance



- Tevatron continues to perform very well:
 - Almost 4 fb^{-1} delivered by Tevatron as of April 2008
 - More than 3 fb^{-1} recorded by CDF

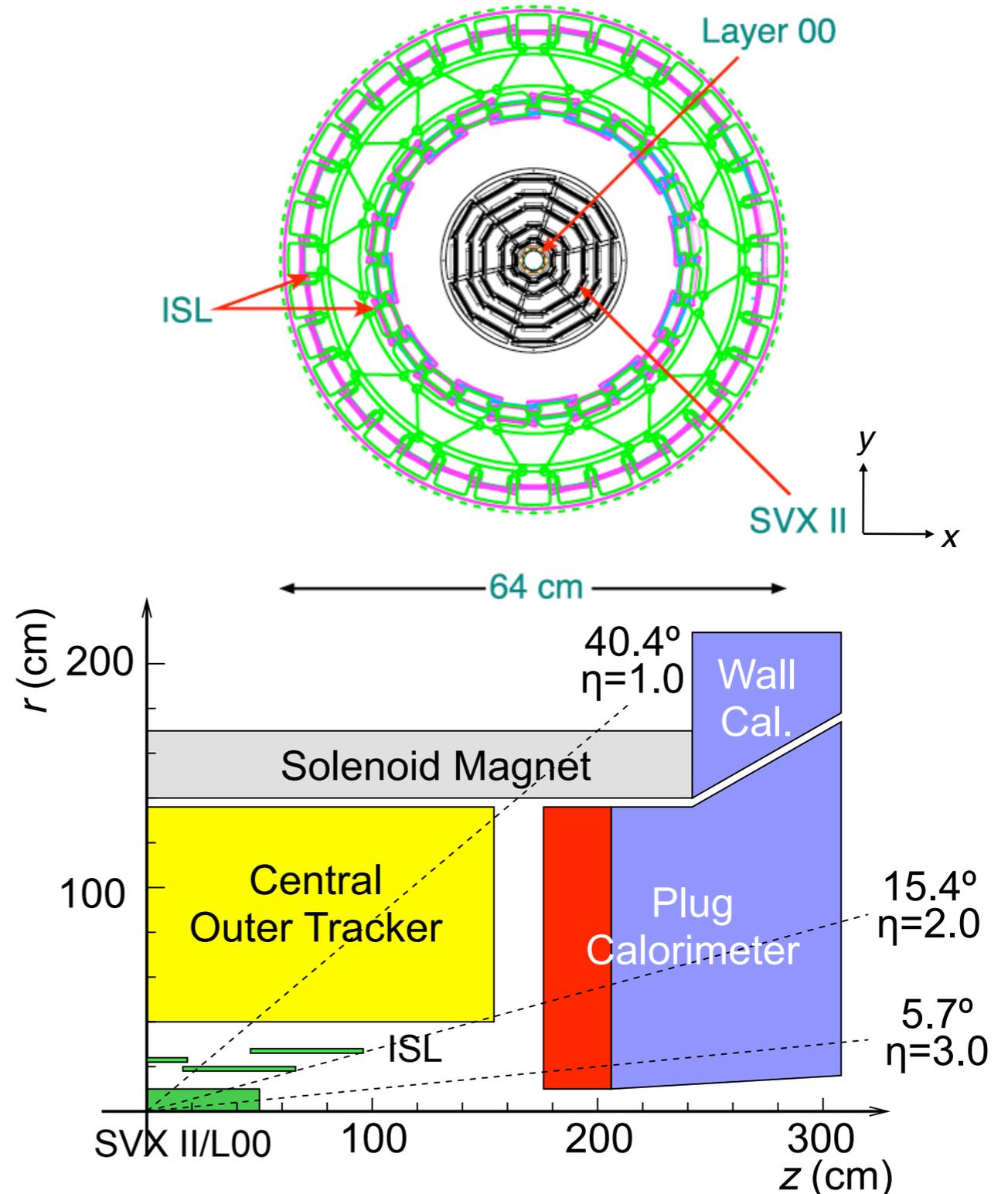




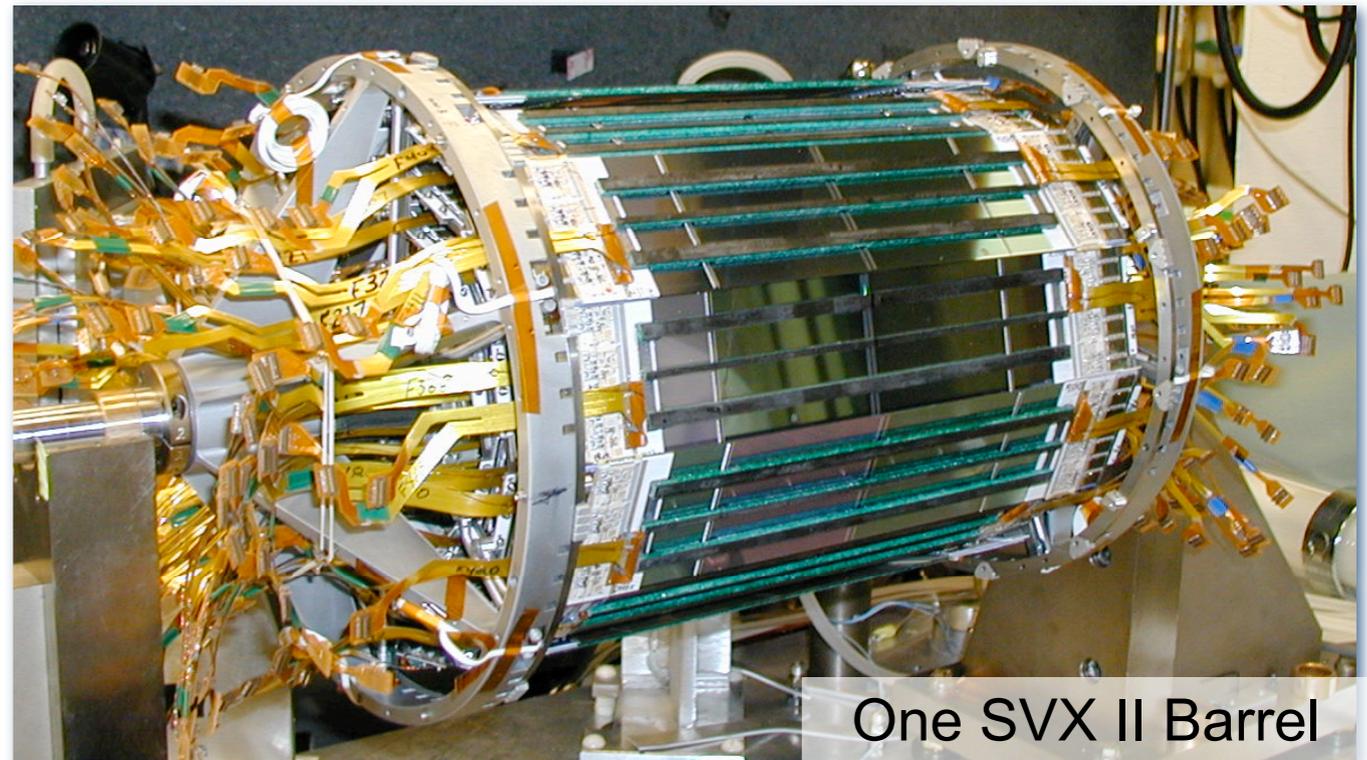


- Level 1 Trigger:
 - Synchronous hardware trigger
 - Input rate: 1.7 MHz
- Level 2 Trigger:
 - Hardware & software triggers
 - Input rate: up to 35 kHz
- Level 3 Trigger:
 - PC farm
 - Input rate: up to 1 kHz
- Special role of Silicon detector due to Silicon Vertex Trigger (SVT)
 - Silicon information used in SVT, i.e. at Level 2
 - must be read out at Level 1

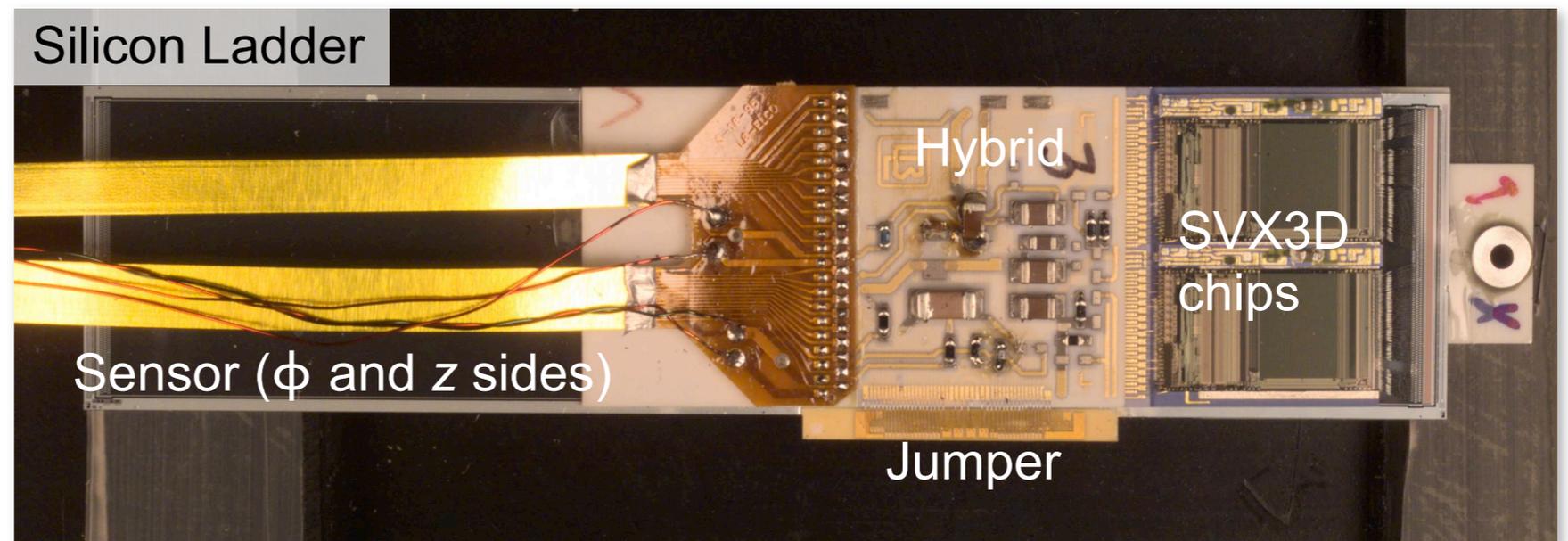
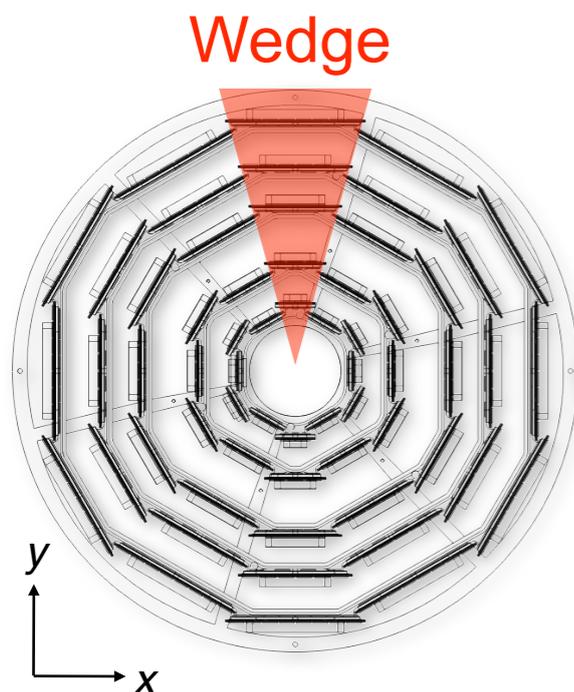
- 7–8 silicon layers (6 m^2)
- 722,432 readout channels on 5,456 readout chips
- Three sub-detectors:
 - SVX II
 - Intermediate Silicon Layers (ISL)
 - Layer 00 (L00)
- Purpose:
 - Precision tracking
 - Reconstruction of primary and secondary vertices

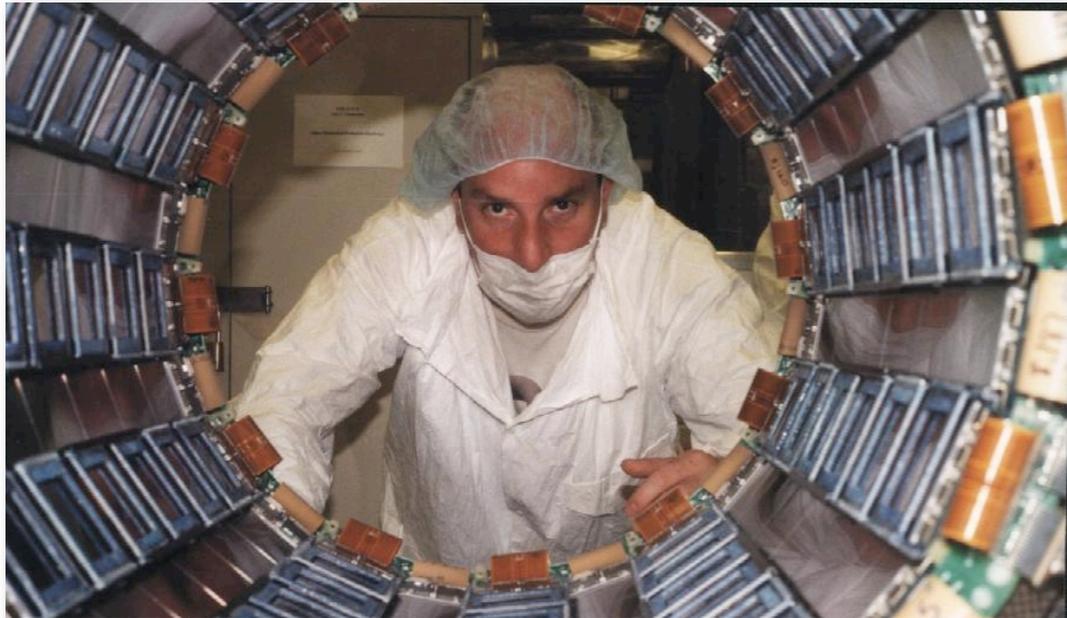


- Mechanical structure:
3 barrels with 6 bulkheads,
12 wedges each (1m long)
- **5 layers of double-sided**
silicon sensors at radii of
2.5–10.6 cm
- Layers 0, 1, 3 (Hamamatsu):
axial and 90° strips
- Layers 2 and 4 (Micron):
axial and 1.2° stereo strips
- Strip pitch: 60–140 μm
- **AC-coupled** readout: micro-
discharges limit bias voltage
to 170 V (Hamamatsu) and
80 V (Micron)



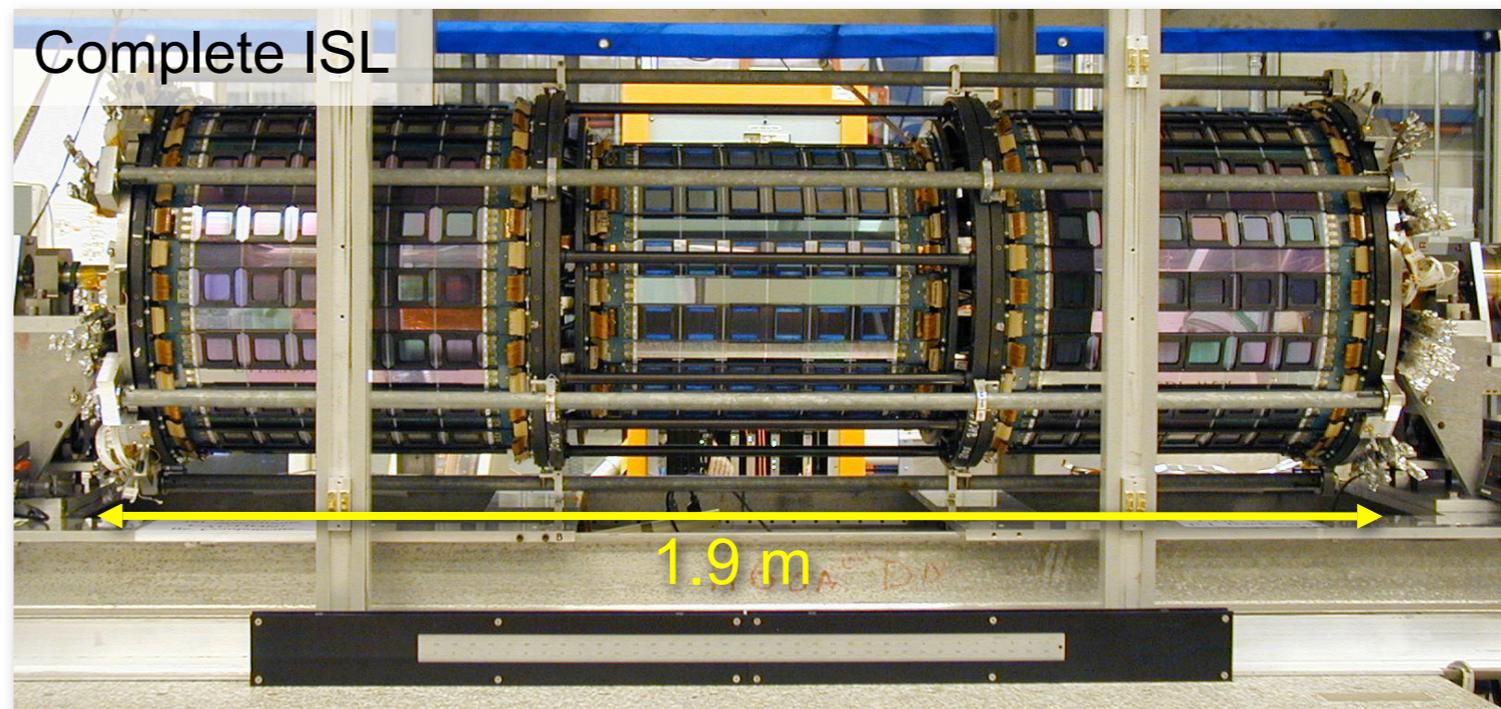
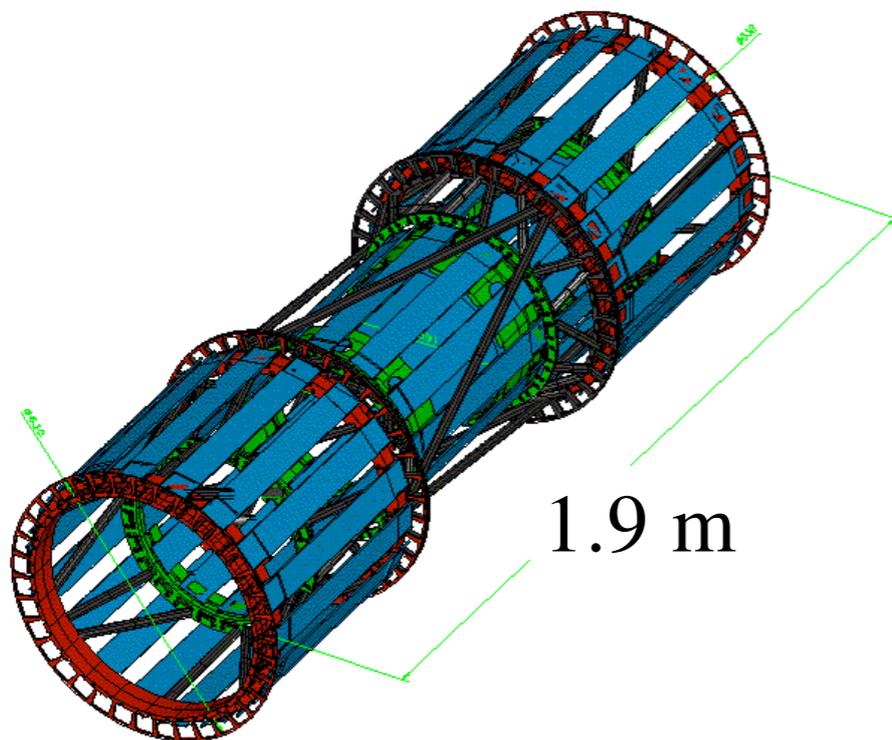
- Silicon Vertex Trigger (SVT):
 - Fast track reconstruction and cut on impact parameter at trigger level
 - Essential for trigger on hadronic B decays
- Requirements for using SVX II in the SVT:
 - Easy geometrical mapping: symmetric 12-fold wedge structure
 - Full SVX II data available at L2: fast readout
 - Tight alignment constraints: SVX II must be parallel to the beam to within $100 \mu\text{rad}$



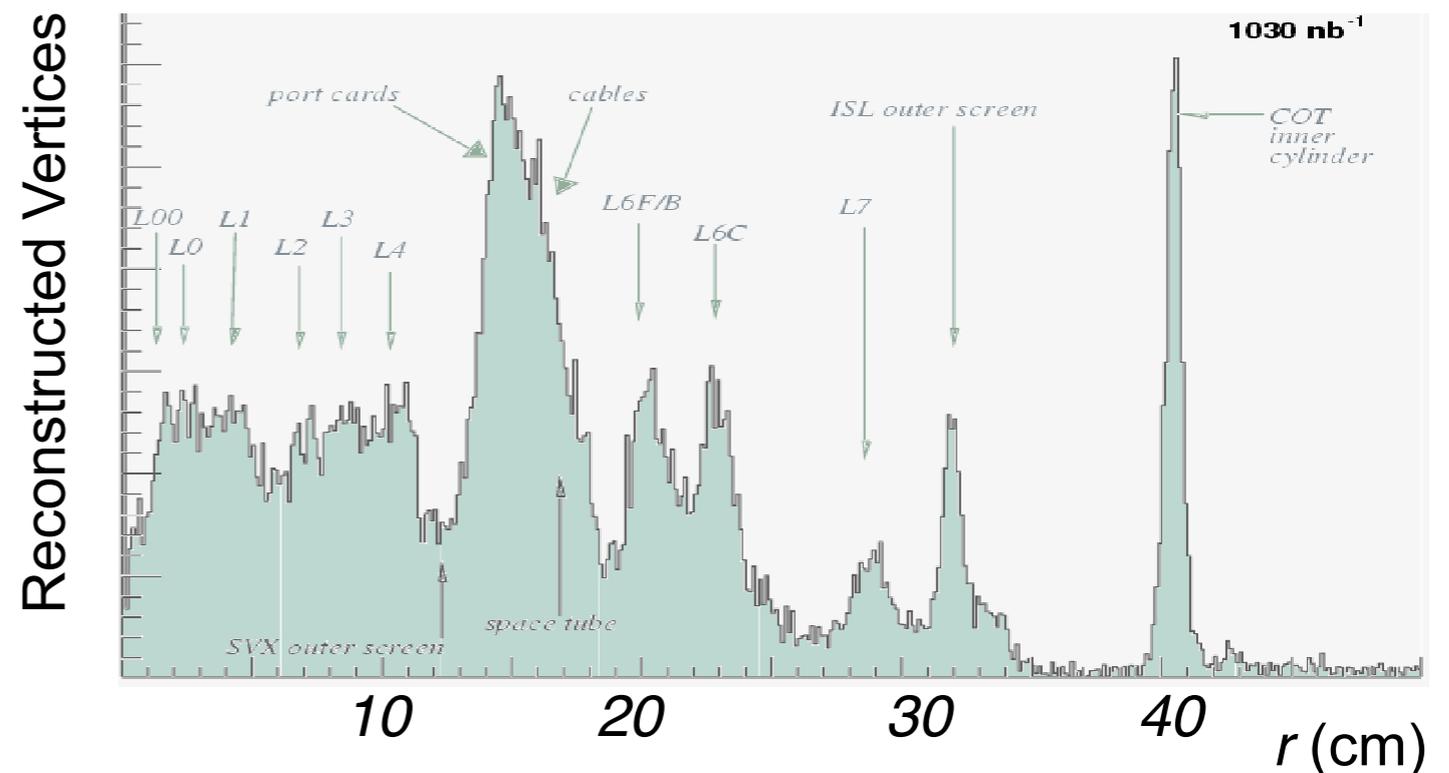


J. Goldstein: "Don't mess with my detector!"

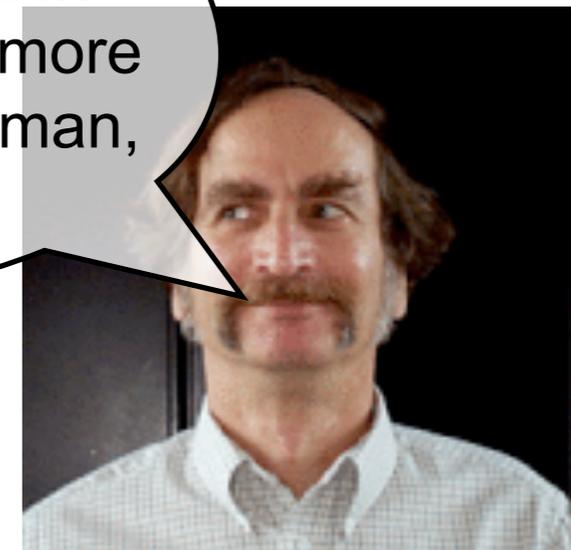
- One central layer ($|\eta| < 1$): **link tracks** from SVX II to wire chamber
- Two forward layers ($1 < |\eta| < 2$): tracking at **large pseudorapidities**
- Strip pitch: $112 \mu\text{m}$



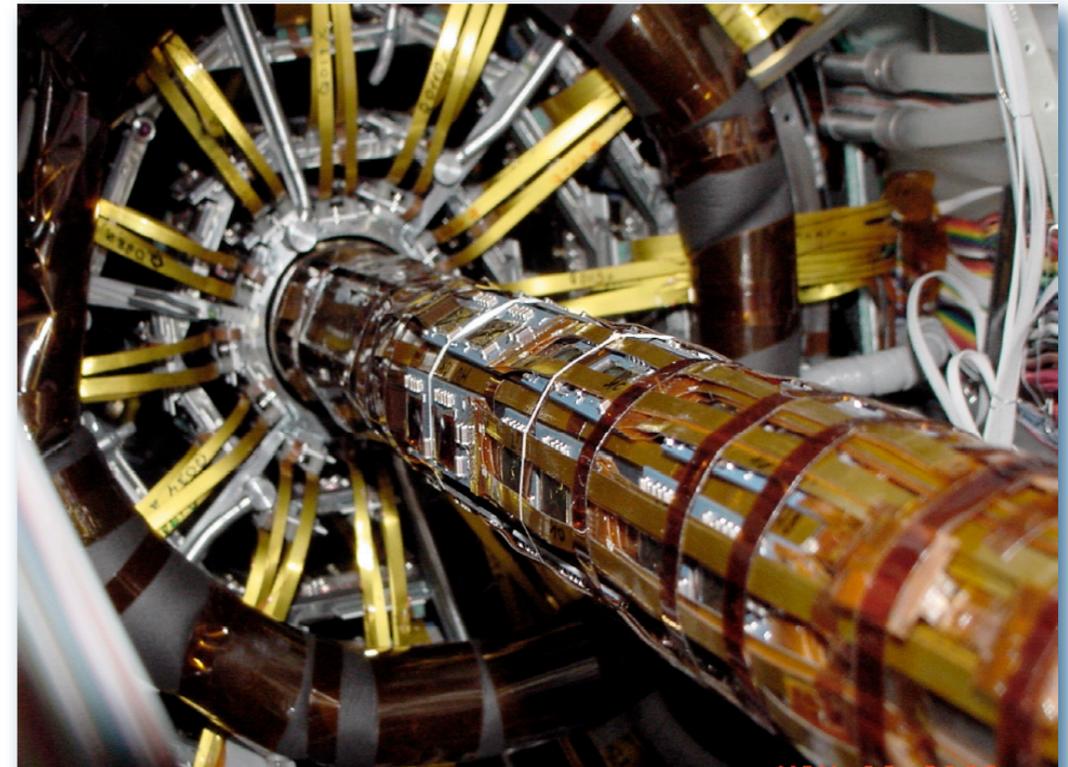
- SVX II: cables, hybrids, portcards, and beryllium bulkheads introduce **a lot of material**
- Poor impact parameter resolution for low- p_T tracks
- Affects also high- p_T physics: need low- p_T tracks for b -tagging
- LHC-style radiation-hard silicon not yet available when SVX II was designed
 - Inner layers may **die of radiation damage**
- Solution: Layer 00
 - New low-mass layer **directly on the beam pipe**
 - Use **radiation-hard silicon**



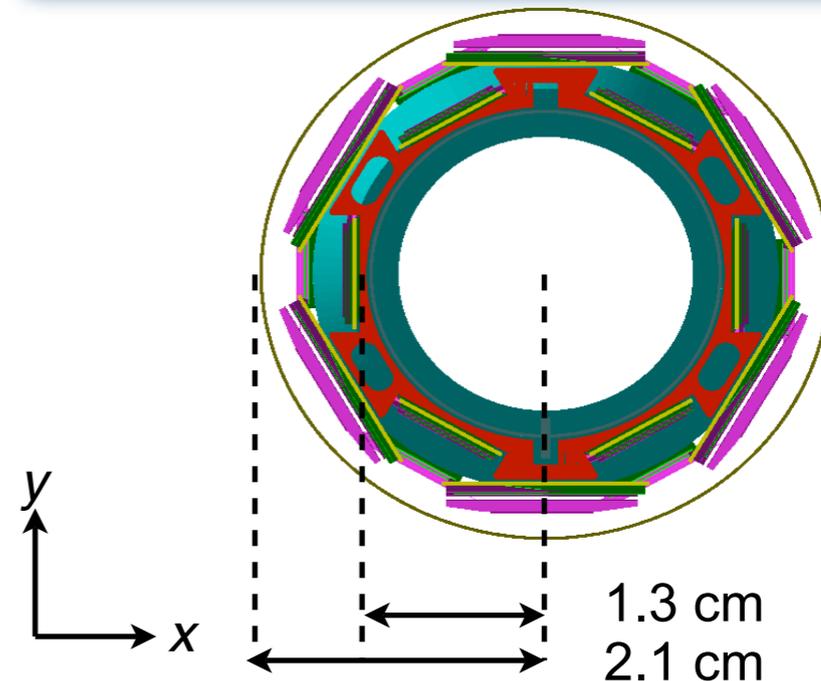
How do you fix a problem of too much material by adding more material? (L. Nodulman, 1997)

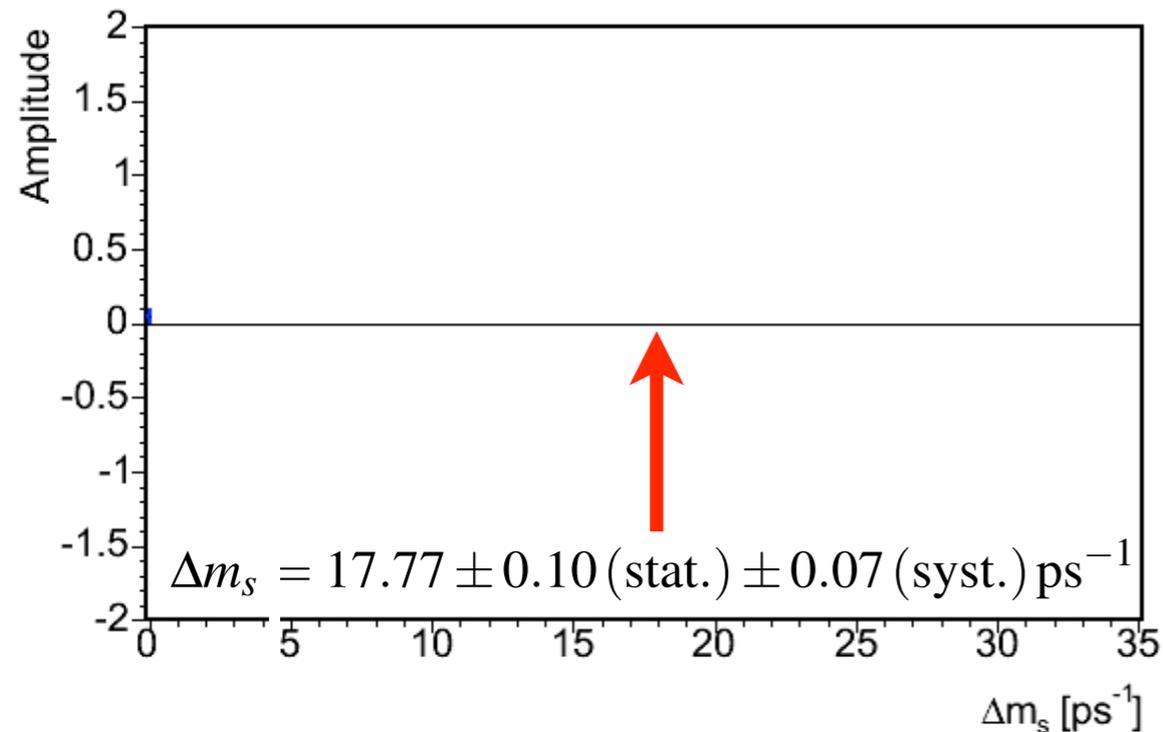


- Material budget:
 - Goal: $0.01 X_0$ (achieved)
 - Below $r = 2$ cm, $0.01 X_0$ of additional material does not matter
- Material and radiation:
 - Remove readout electronics from tracking volume
 - Transmit **analog signals** to chips
- Single-sided “**LHC style**” **sensors**:
 - Non-oxygenated (Hamamatsu, SGS Thomson)
 - Oxygenated (Micron)
- **Actively cooled** support structure
- Strip pitch: $25 \mu\text{m}$, every second strip read out



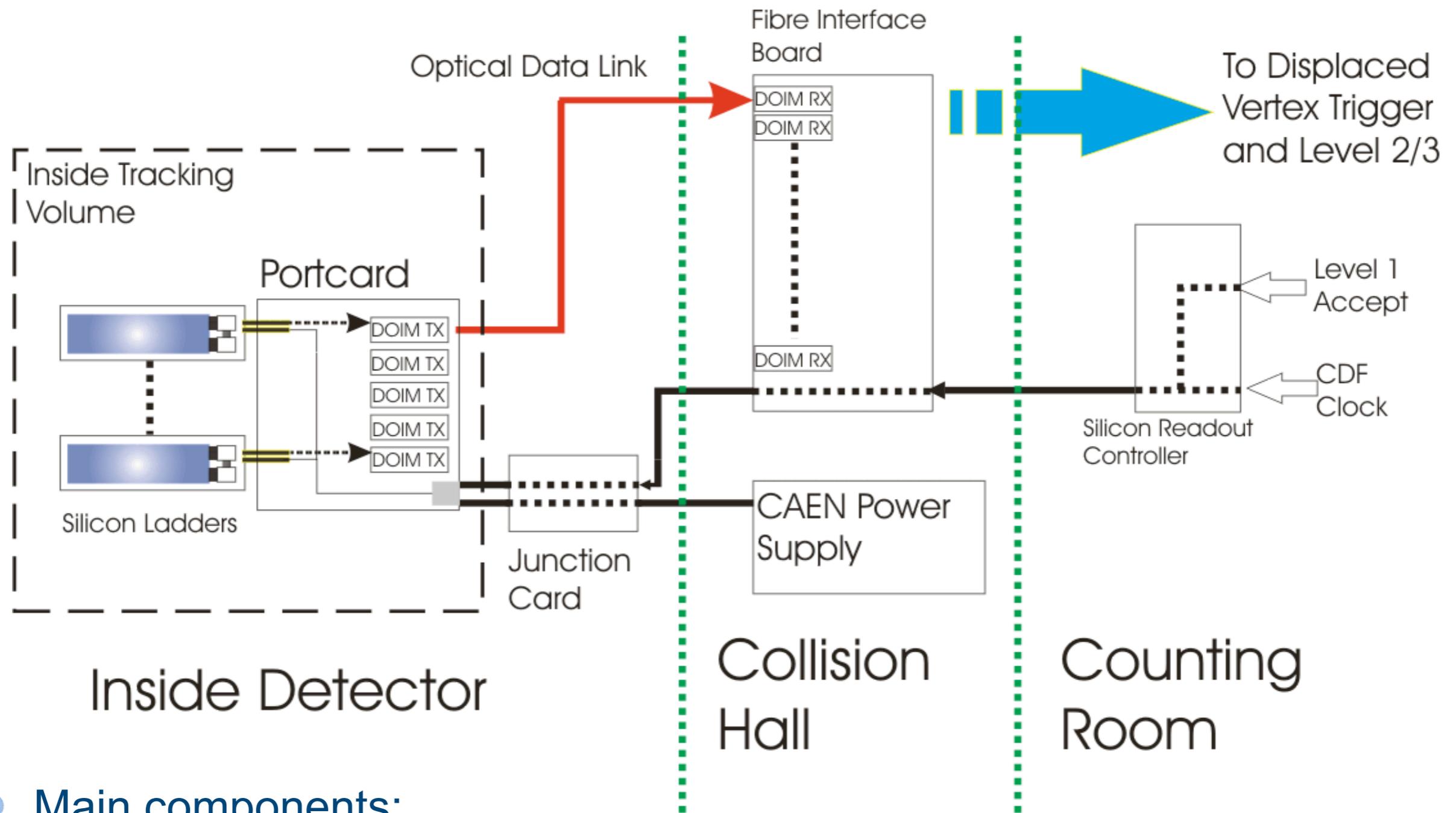
NOV 23 2000
Insertion of L00: $300 \mu\text{m}$ clearance!





[Aart Heijboer, U. of Pennsylvania]

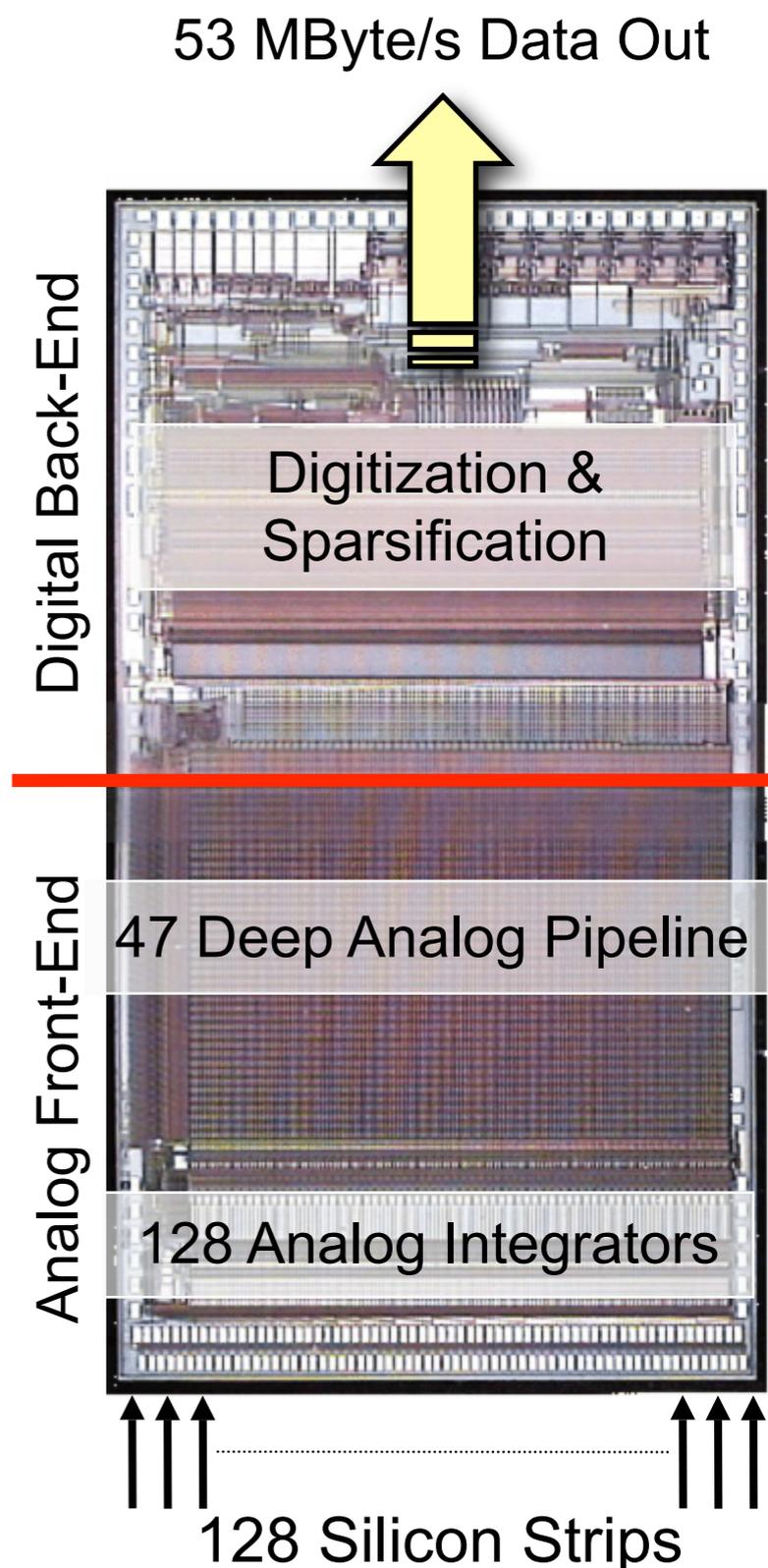
- Discovery of B_s oscillations: Phys. Rev. Lett. **97** (2006) 242003
- Layer 00 makes the difference: uncertainty on oscillation amplitude **reduced by factor of >2** → **5 σ discovery** instead of 3 σ evidence
- Achieved decay time resolution of **$\sigma_t = 90 \text{ fs}$** (1/4 of measured oscillation period)
- Resolution corresponds to approx. **27 μm decay length resolution**



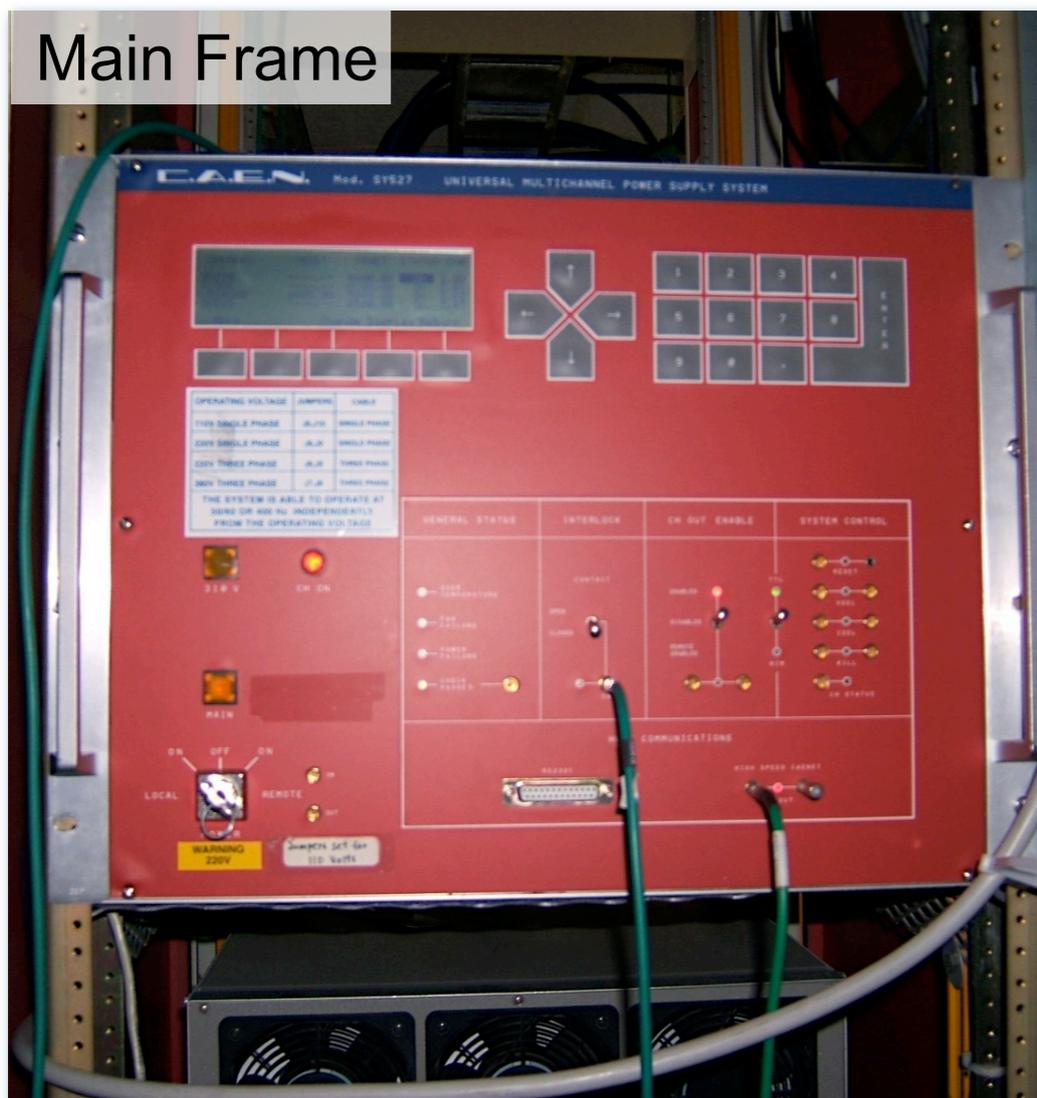
- Main components:

- **Silicon Readout Controller (SRC):** “brain” of the system
- **Fiber Interface Board (FIB):** control signals and optical readout
- **Portcard:** chip commands and optical transmitters (DOIMs)

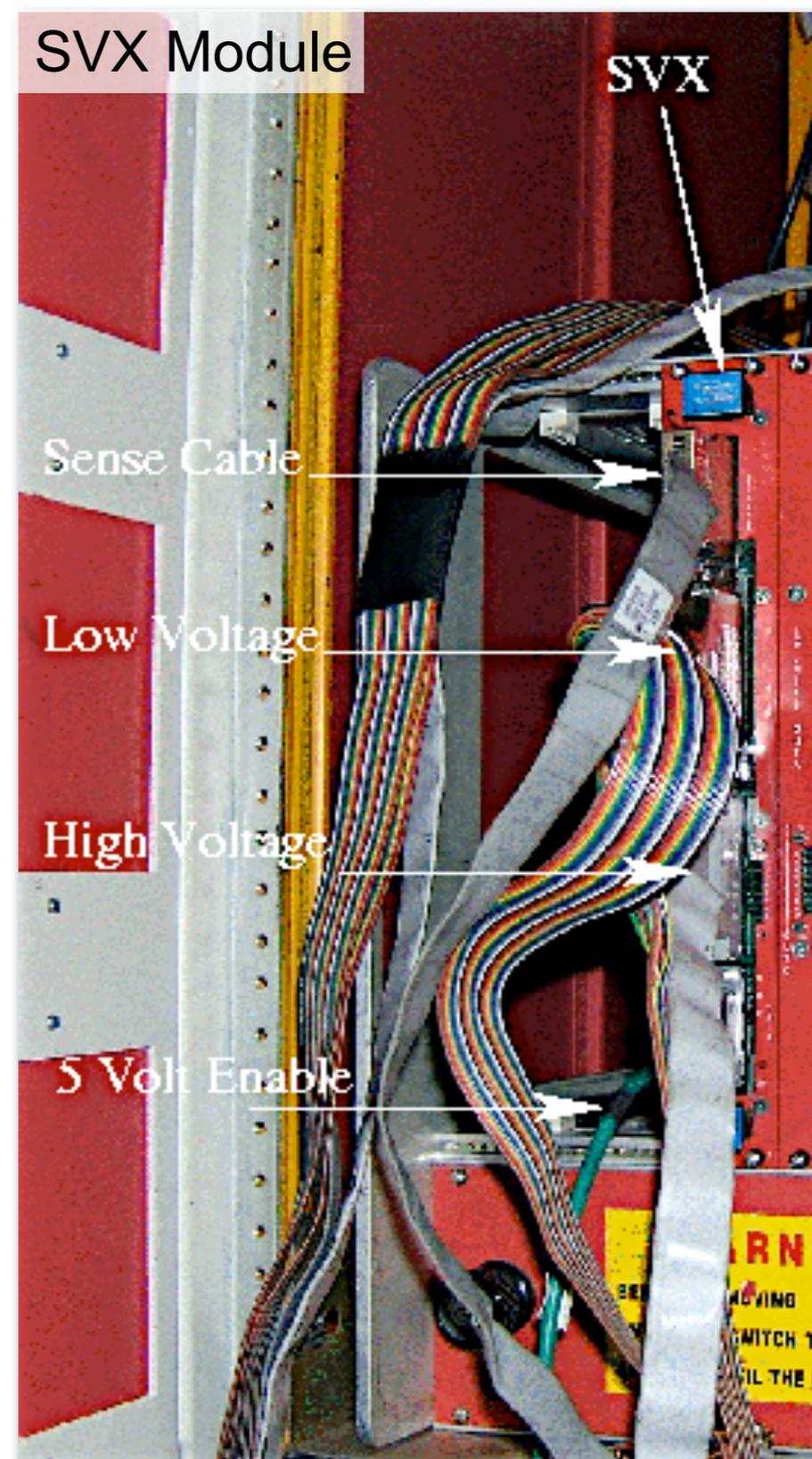
- Integrated analog front-end and digital back-end
- **Fast**: capable of running at 132 ns clock rates
- **Deadtimeless**: can collect charge and digitize simultaneously
- **Dynamic pedestal subtraction**
 - On-chip subtraction of common mode noise (defined as number of ADC counts measured in 31st lowest channel)
- On-chip **sparsification**
 - Removes channels below programmable threshold
 - Reduces data rate and readout time
- Honeywell **radiation-hard** CMOS 0.8 μm process, irradiated with:
 - 40 kGy with ^{60}Co source: 17% chip noise increase
 - 150 kGy with 55 MeV Proton source



Main Frame

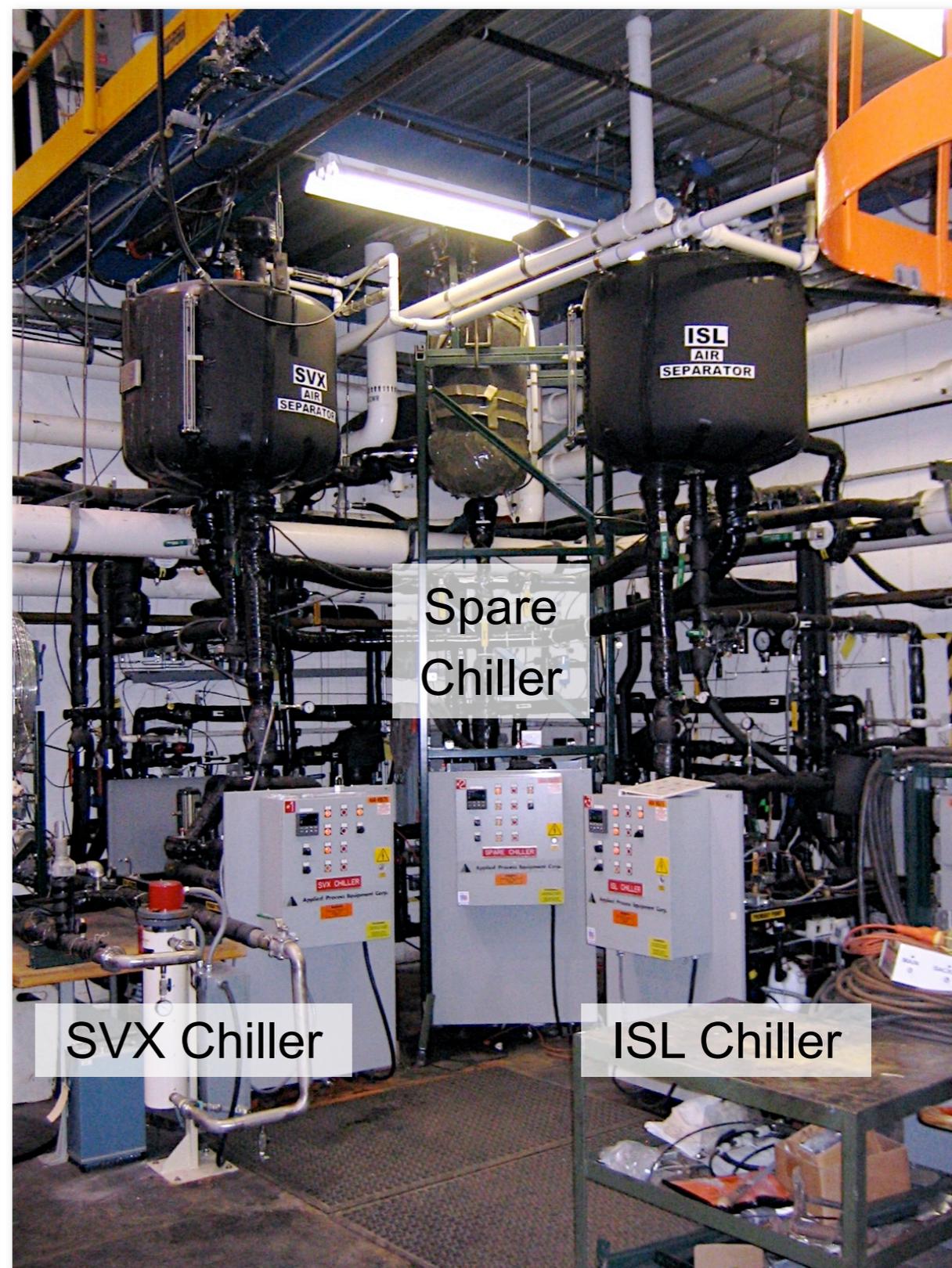


SVX Module

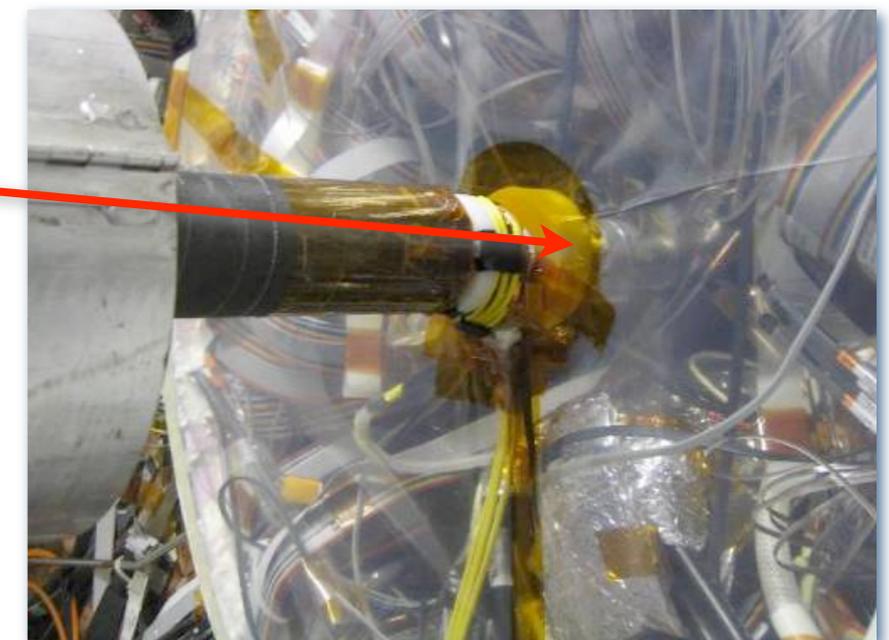
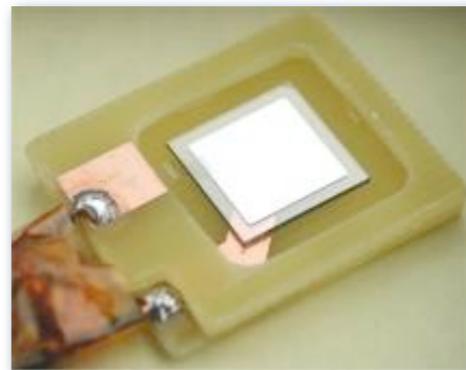
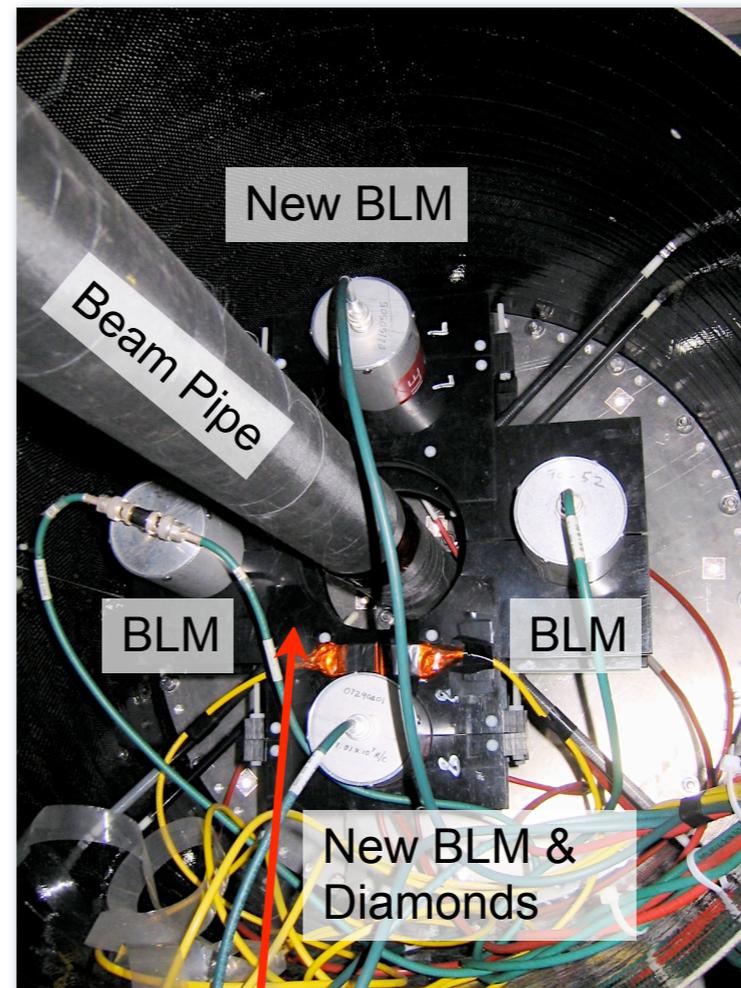


- Standard CAEN SY527 main frame & custom modules
- Installed in collision hall
- CAENet communication

- Readout electronics develops **3.5 kW of heat**
- Low temperatures are **beneficial** for Silicon sensors:
 - Reduction of **thermal noise**
 - Mitigation of **radiation damage**
- Solution: operate Silicon detectors at **-10 °C** (SVX II/L00) and **+6 °C** (ISL, electronics)
- System runs sub-atmospheric
- Protect Silicon by **interlock system** based on Programmable Logic Controller
 - Monitor several 100 **process parameters**: temperatures, pressures, dew points, ...
 - **Trip chillers & power supplies** in unsafe situations

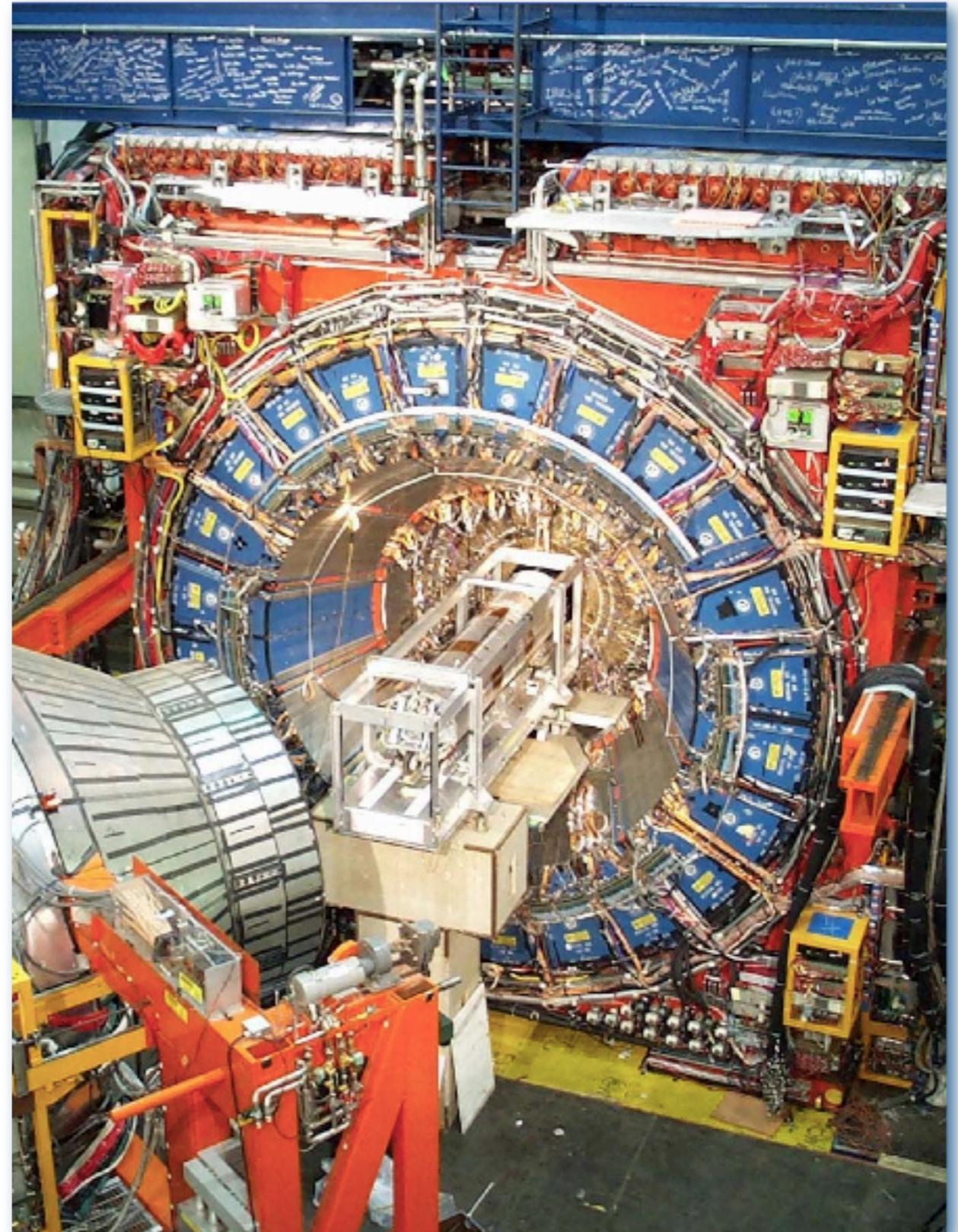


- Traditional system:
 - 4 Beam Loss Monitors (BLMs)
 - CAMAC logic **triggers beam abort** if dose rate > 0.12 Gy/s
 - Time resolution ($210 \mu\text{s} = 10$ Tevatron revolutions) **too slow** for some beam incidents
- Diamond/BLM upgrade (operational since Summer 2007)
 - Faster **VME electronics**: $21 \mu\text{s} = 1$ revolution
 - Smaller & closer to Silicon real estate: polycrystalline CVD **diamond detectors**

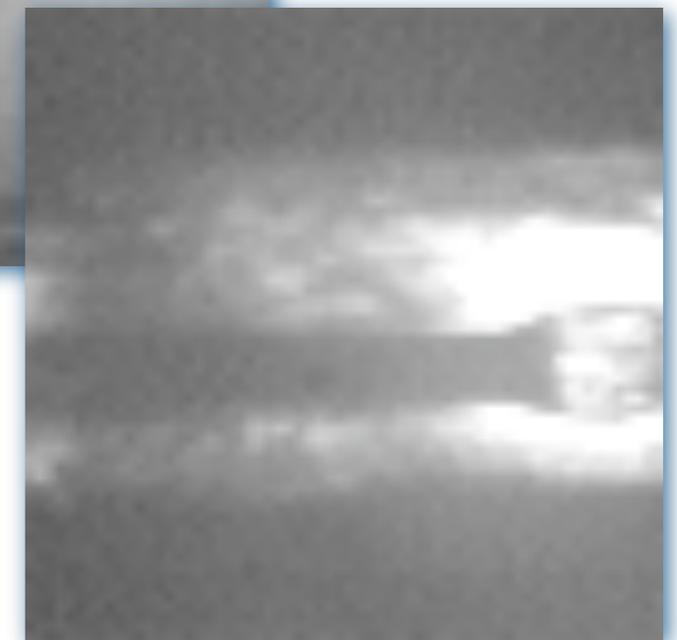
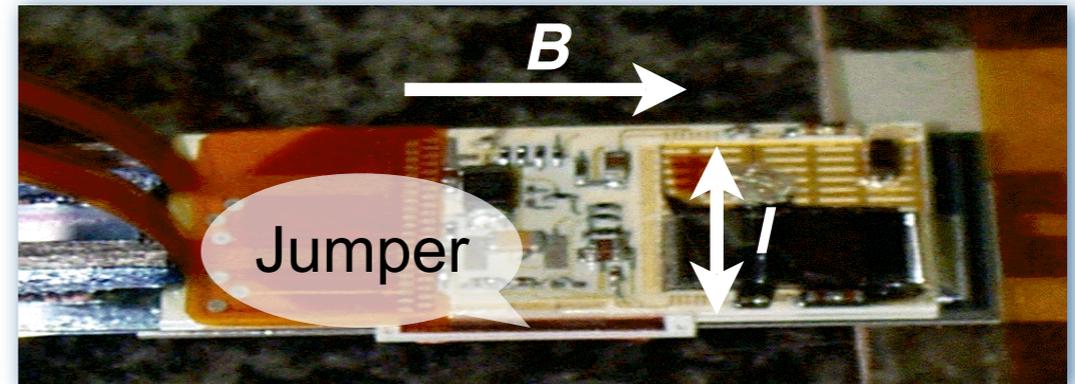




- Timeline:
 - R&D: 4 years
 - Production & Installation: 1 year
 - Commissioning: 1.5 years
- Various problems encountered initially:
 - Power supply burn-out
 - Blocked cooling lines in ISL
 - Noise pickup on L00
 - **Wirebond resonance problems**
 - Beam incidents
- All of the above problems have been addressed: detector in **good shape** for Run II



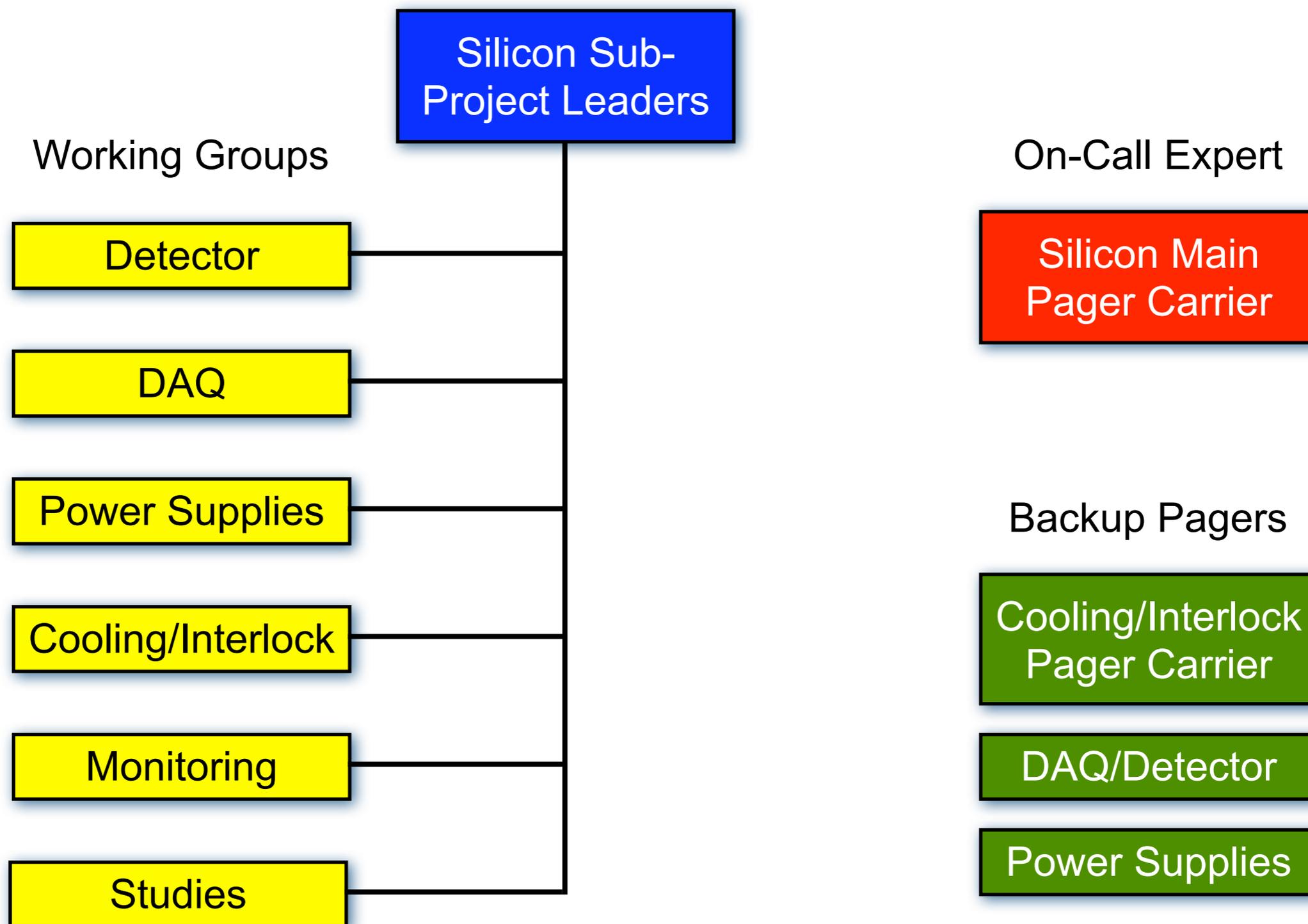
- Symptom: mysterious **loss of z sides**
- Reason (reproduced on test bench):
 - Wires in jumper to connect $r-\phi$ and z sides are perpendicular to magnetic field → **Lorentz force**
 - Highest current during readout
 - **Resonance** frequency around 20 kHz
- Preventing further losses:
 - **Dedicated VME board** to measure Δt between subsequent readout commands → stop data-taking if more than 13 readout commands with the same Δt occur
 - **Limit L1 trigger rate** to < 35 kHz
- ATLAS and CMS learnt the lesson:
 - Resonance protection board (ATLAS)
 - Potted wires (CMS)





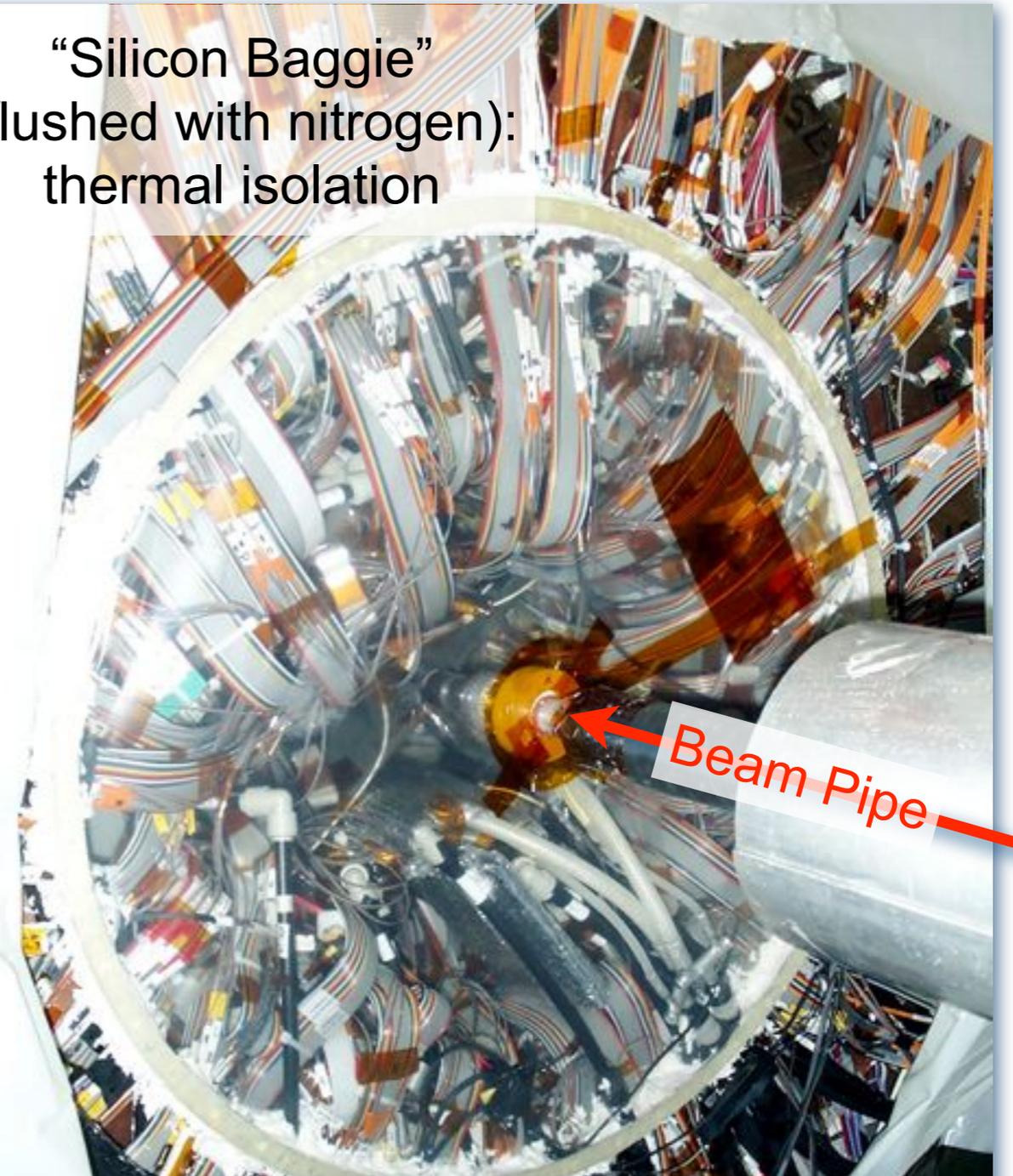


Silicon Operations Group



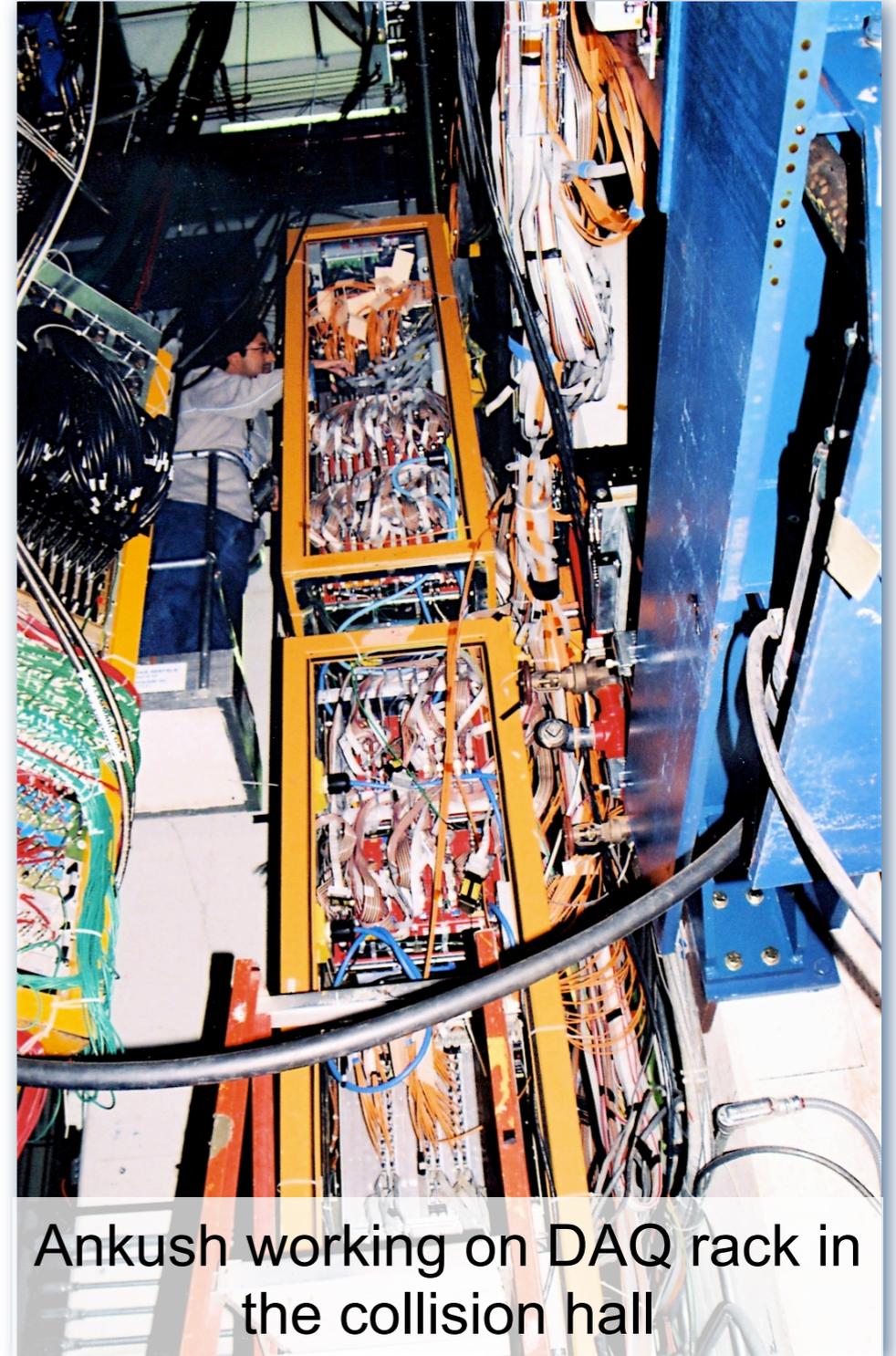
- A **complex** system...
 - 722,000 channels
 - 5,400 chips
 - 135 VME boards in 17 crates
 - 114 power supplies in 16 crates
 - Cooling & interlocks
 - Lots of cables
- ... and **not very accessible**:
 - Power supplies and part of DAQ in collision hall
 - Detector and portcards: inaccessible

“Silicon Baggie”
(flushed with nitrogen):
thermal isolation



COT face during a plug calorimeter pull:
This is as close as we get to the Silicon

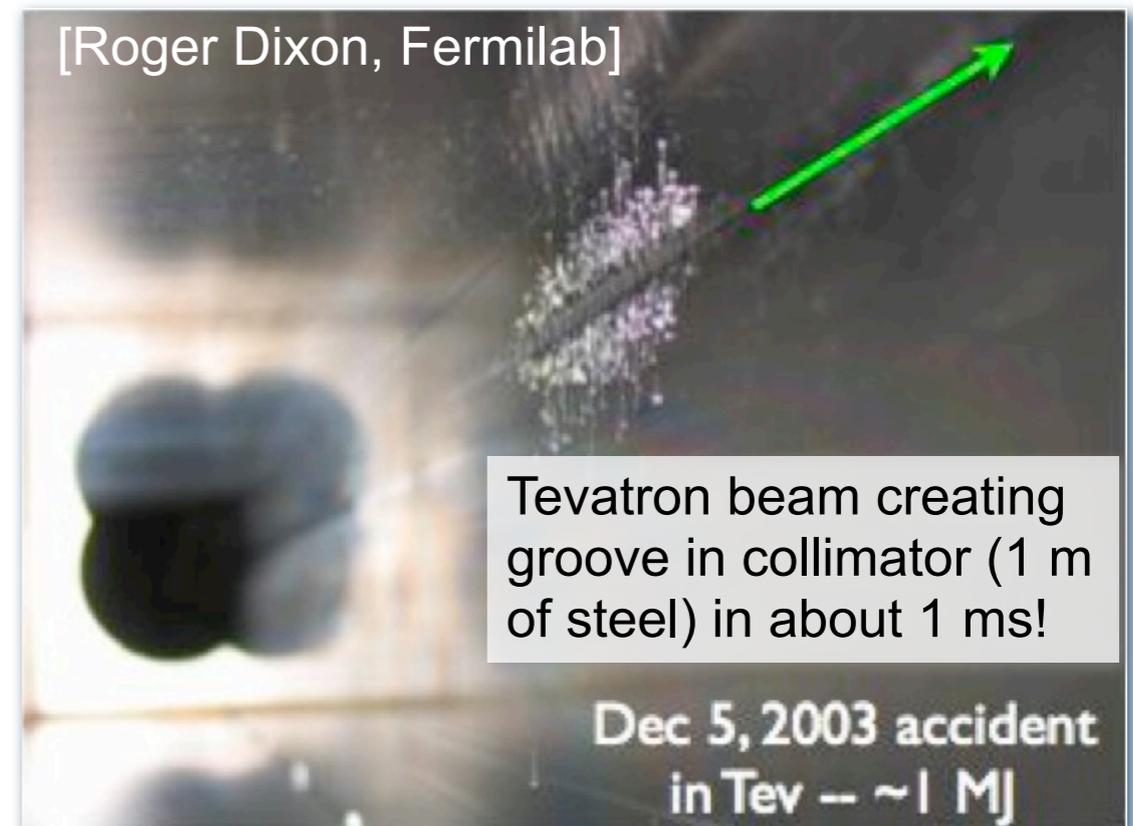
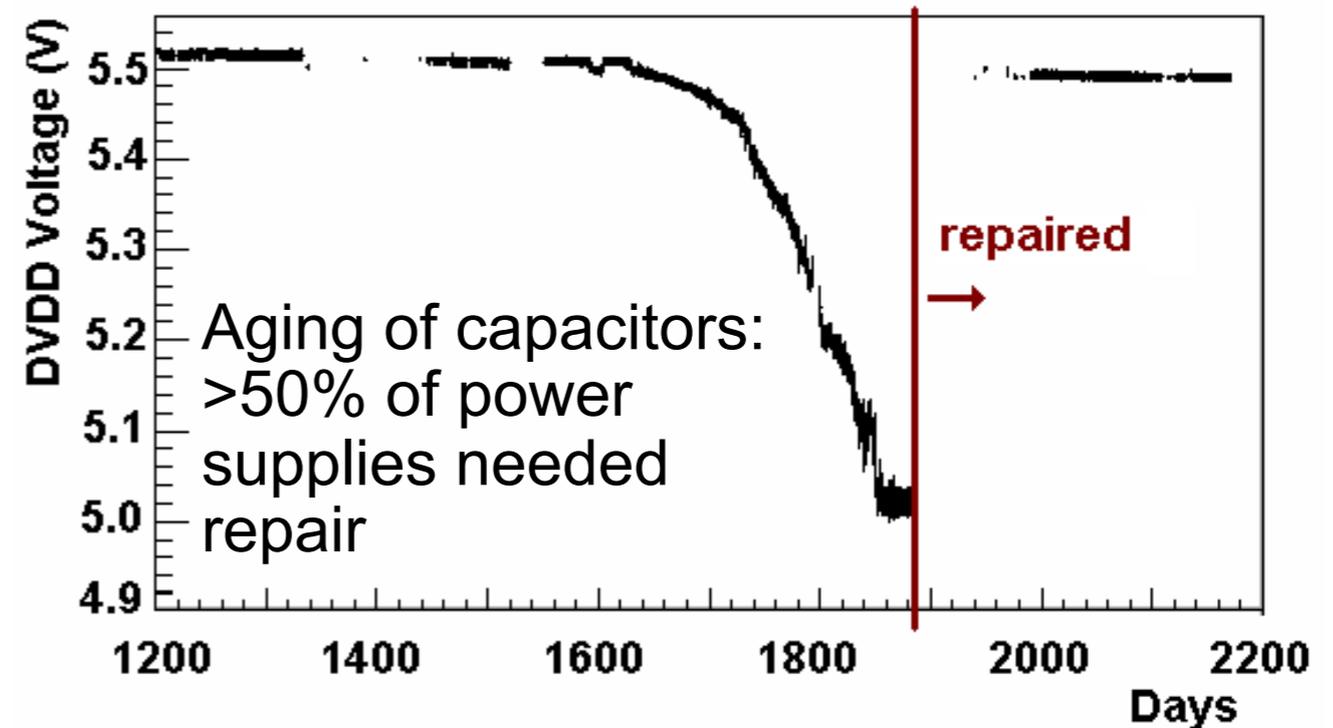
- Maintain **constant high efficiency** due to aggressive “No Ladder Left Behind” policy:
 - Vigilant **monitoring**: spot problems early (digital errors, ADC spectra, ...)
 - Detailed **logging** of problems occurring
 - “**Quiet time studies**”: diagnose problems a.s.a.p. → fix or mitigate
 - Collision hall **access** between stores: diagnosis and exchange of broken equipment
 - **Extremely successful**, but person-power intensive: need 4–6 FTE
- Since 2006: focus on **automatic recovery** of most common failure modes → higher efficiency with fewer people



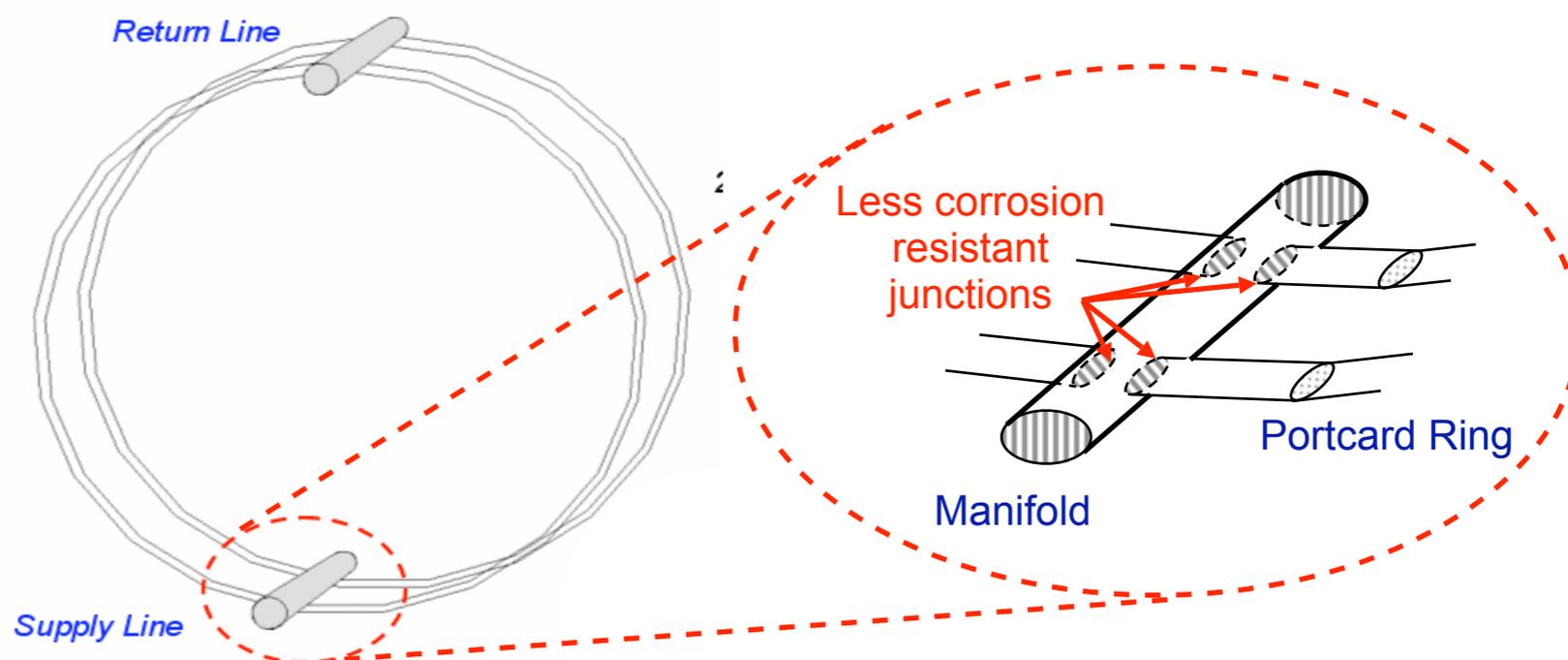
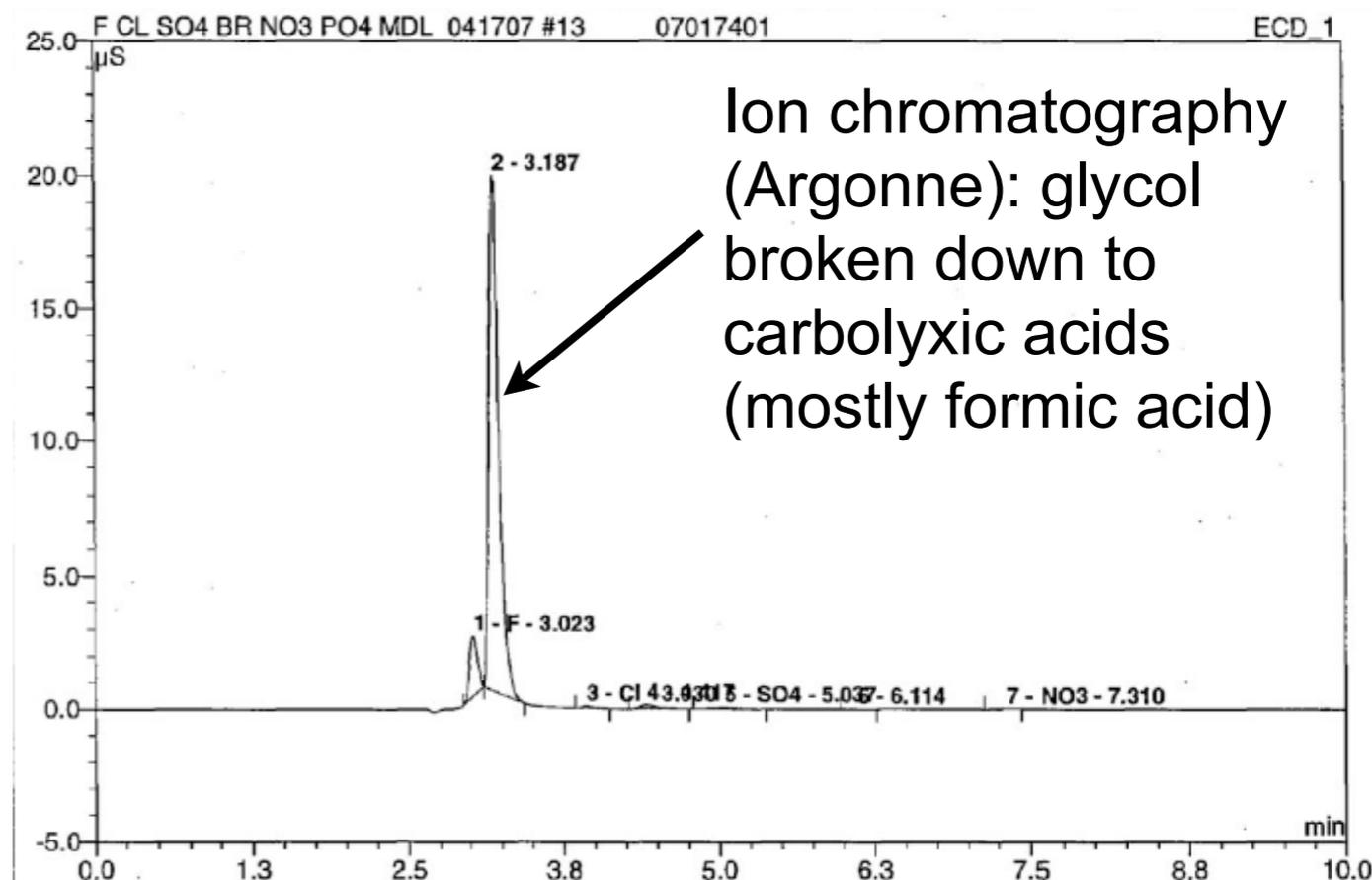
Ankush working on DAQ rack in the collision hall

*see: *No Child Left Behind Act* of 2001 (US Public Law 107-110), also: US Marine Corps motto

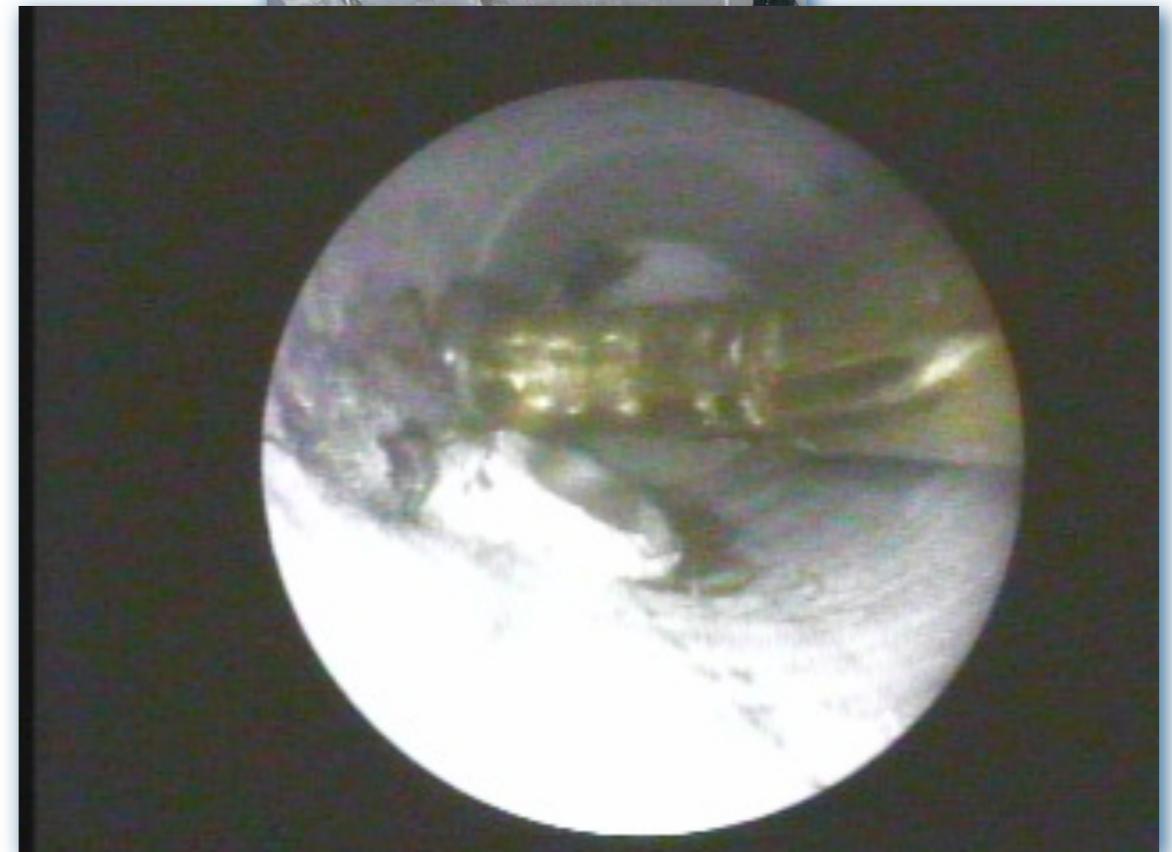
- **Radiation-related:**
 - **Single-event upsets** in collision hall DAQ boards (approx. 1 per day)
 - **FPGA burnout** (1–2 per year)
- **Power supply failures:** corrupted read-back, drooping voltages, spontaneous switch-offs, loss of CAENet communication
- **Beam incidents:**
 - Examples: magnet quenches, RF station loss, beam separator sparks, spontaneous ramping of abort kicker magnets
 - Close collaboration with Tevatron group: reduced to a minimum now
- **Cooling and interlocks:** chiller wear and tear, frozen cooling lines, humidity sensor problems, **leaks**

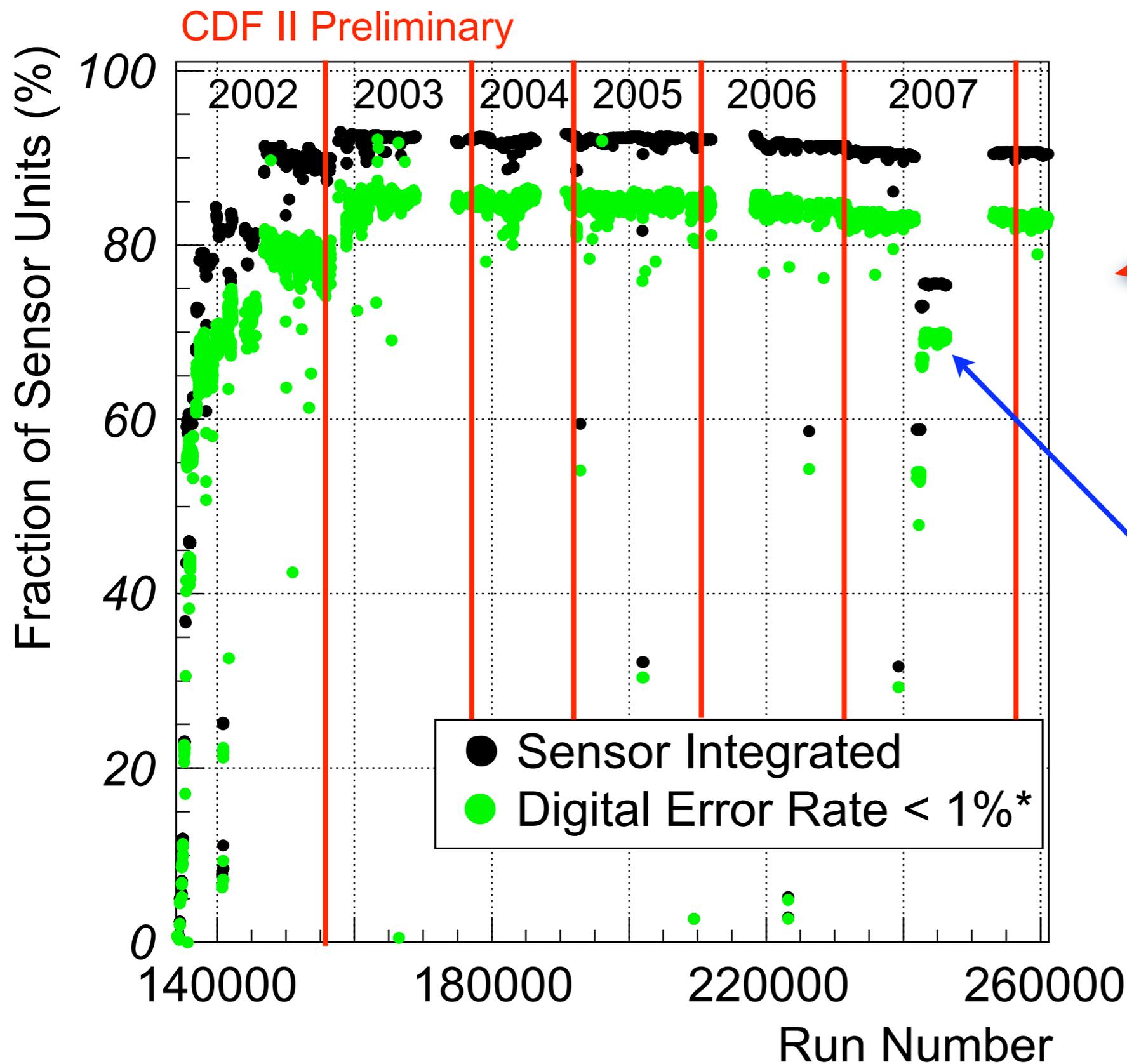


- First symptoms: electronic valve failures (early 2007)
- Problem: ISL coolant (10% ethylene glycol in water) became **acidic** (pH ≥ 2 = vinegar) during 2006 shutdown
- Solution: coolant **neutralized** by drain and flush procedure and large de-ionizers, unfortunately too late...
- ... May 2007: **leaks** in heat affected zone around aluminum welds in ISL Portcard ring (alloy: 6061-Al)



- Repair during 2007 shutdown (1 month of work for 4–5 people)
- Challenge #1: **radiation damage**
 - Must keep Silicon cold (and dry)
 - Solution: set up plastic tent, use air dryer to keep dew point below -10°C at all times
- Challenge #2: Portcard ring **inaccessible** from outside
 - Inside detector, approx. 1 m away from COT face
 - Repair **through cooling tubes** using borescopes, catheters, syringes, ...
 - Cover holes with epoxy using 0.75 mm brass tube
- Result: all leaks fixed, stable running since October 2007

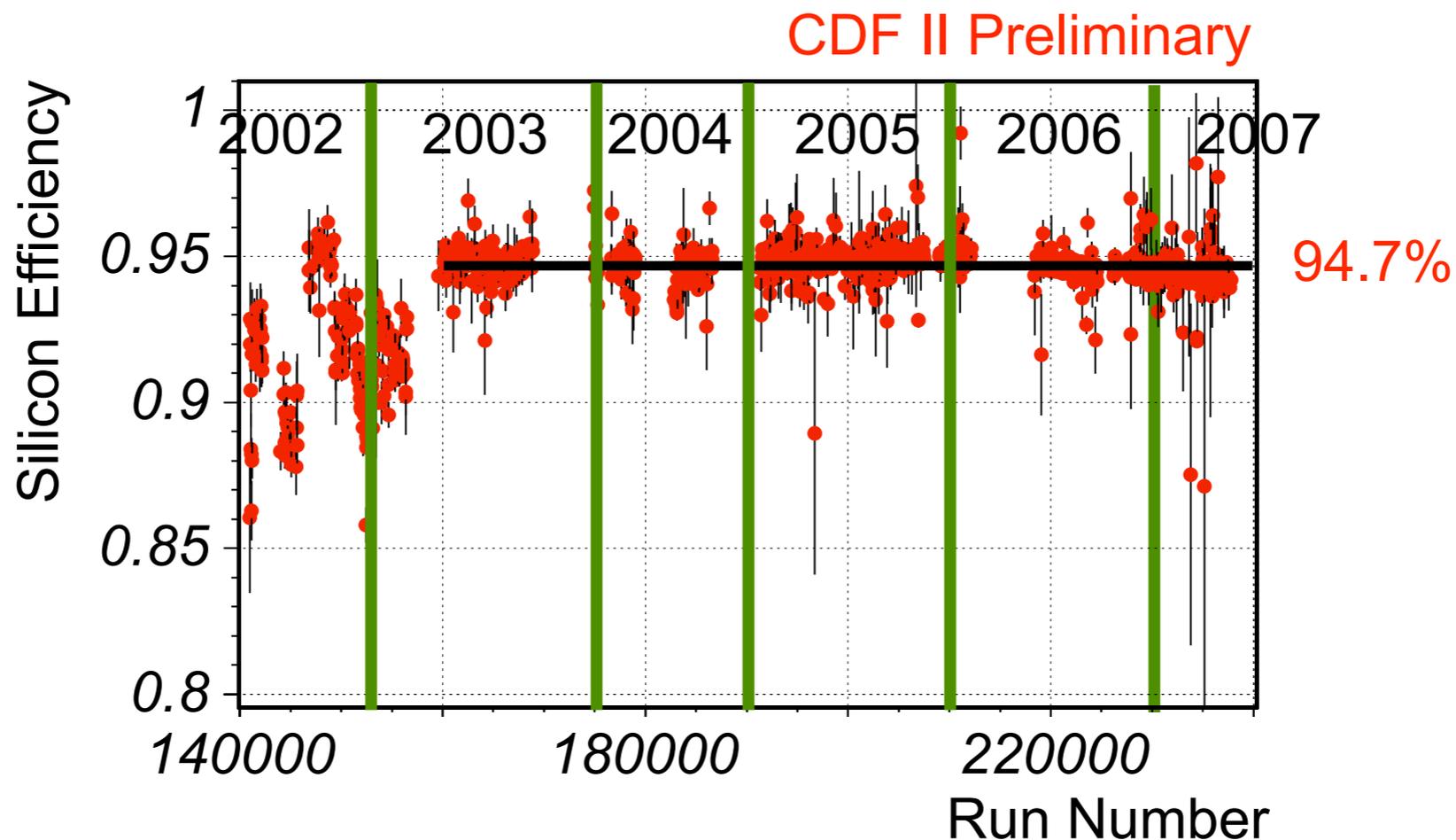




Maintaining High Efficiency

ISL Cooling Leak

*approx. half of the sensor units with digital errors can be recovered offline



- **Very stable efficiency** after commissioning, **average: 95%**
- Define efficiency as close as possible to standard CDF tracking:
 - Denominator: muons from $J/\psi \rightarrow \mu\mu$ with muon ID and COT track which cross at least 3 layers of SVX II
 - Numerator: Silicon added to COT track by standard pattern recognition, at least 3 layers with hits in SVX II/L00

[...] because as we know, there are **known knowns**; there are things we know we know. We also know there are **known unknowns**; that is to say we know there are some things we do not know. But there are also **unknown unknowns** — the ones we don't know we don't know.
(D. Rumsfeld, 2002)



- **Expect surprises** during commission and operation
- Keep **expertise** around, good documentation
- Eliminate **single points of failure**: what can break will break
- **Spares**, spares, spares...
- It's a **hadron collider**, dude! Don't underestimate **radiation-induced failures** and beam incidents
- Don't forget **infrastructure**: cables, power supplies, cooling, ...





Silicon Detector Longevity



- Performance of key components **decreases with irradiation**, main concern: **inner detector layers**
- **Noise increase**
 - Bulk damage of sensors: increased leakage currents & capacitance
 - Electronics: chip damage, capacitance
- **Signal degradation**
 - Charge trapping in crystal defects: decreased charge collection efficiency
 - Bias voltage limited: under-depletion of sensors

Component	Performance after 8 fb ⁻¹
Optical Transmitters	10% degradation of light level, no change in wave form
SVX3D Readout Chip	17% noise increase
Silicon Sensors	This talk

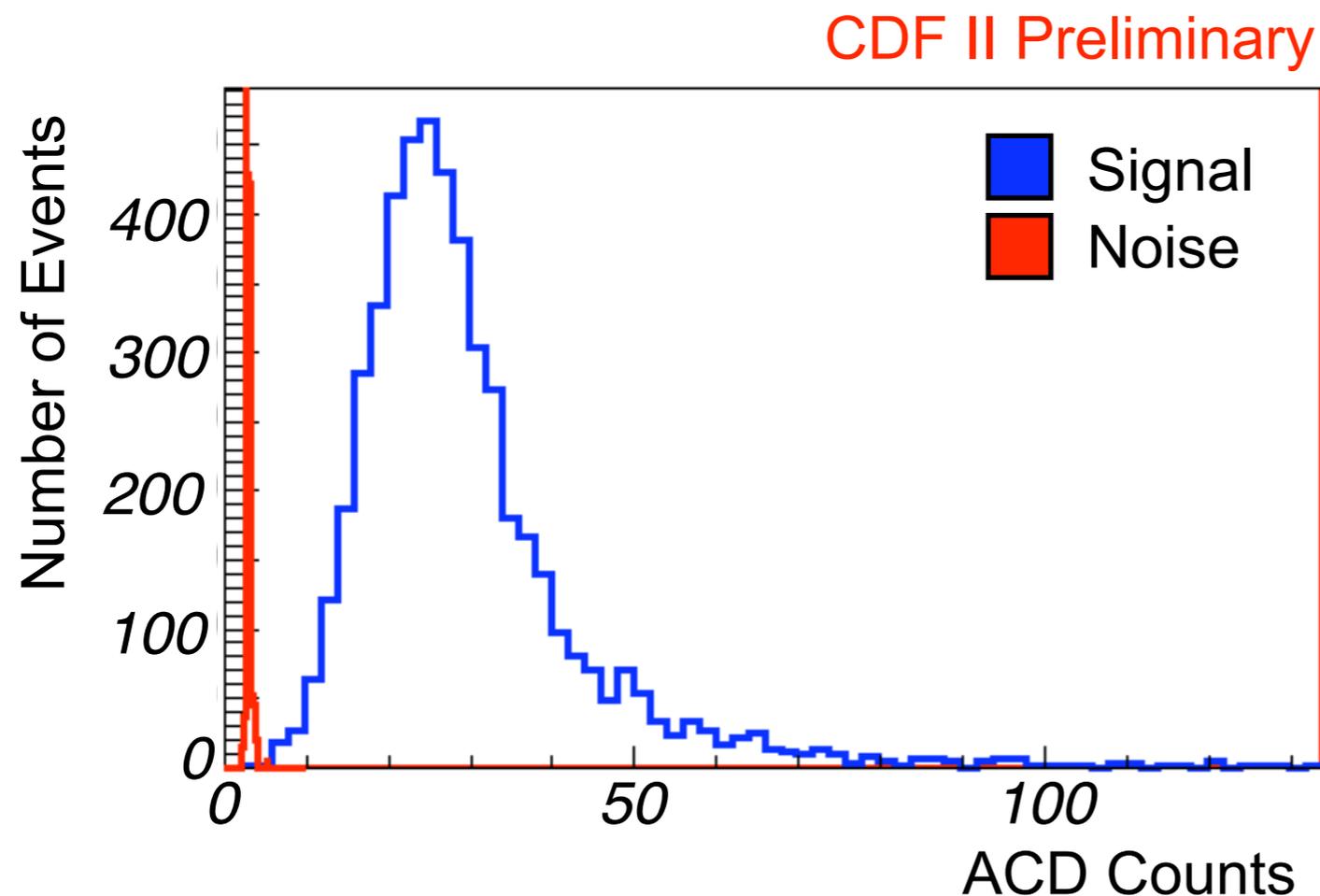
- Two main sources of noise:

- Sensor **shot noise** (I_{leak} = leakage current): $Q_{\text{shot}} = 900 e^{-} \sqrt{I_{\text{leak}} (\mu\text{A})}$

- Chip noise** (C_{chip} = chip capacitance): $Q_{\text{chip}} = f_1(\Phi) + f_2(\Phi) C_{\text{chip}}$

Test beam data: 17% increase of chip noise after 8 fb⁻¹

- Direct measurement** from data:

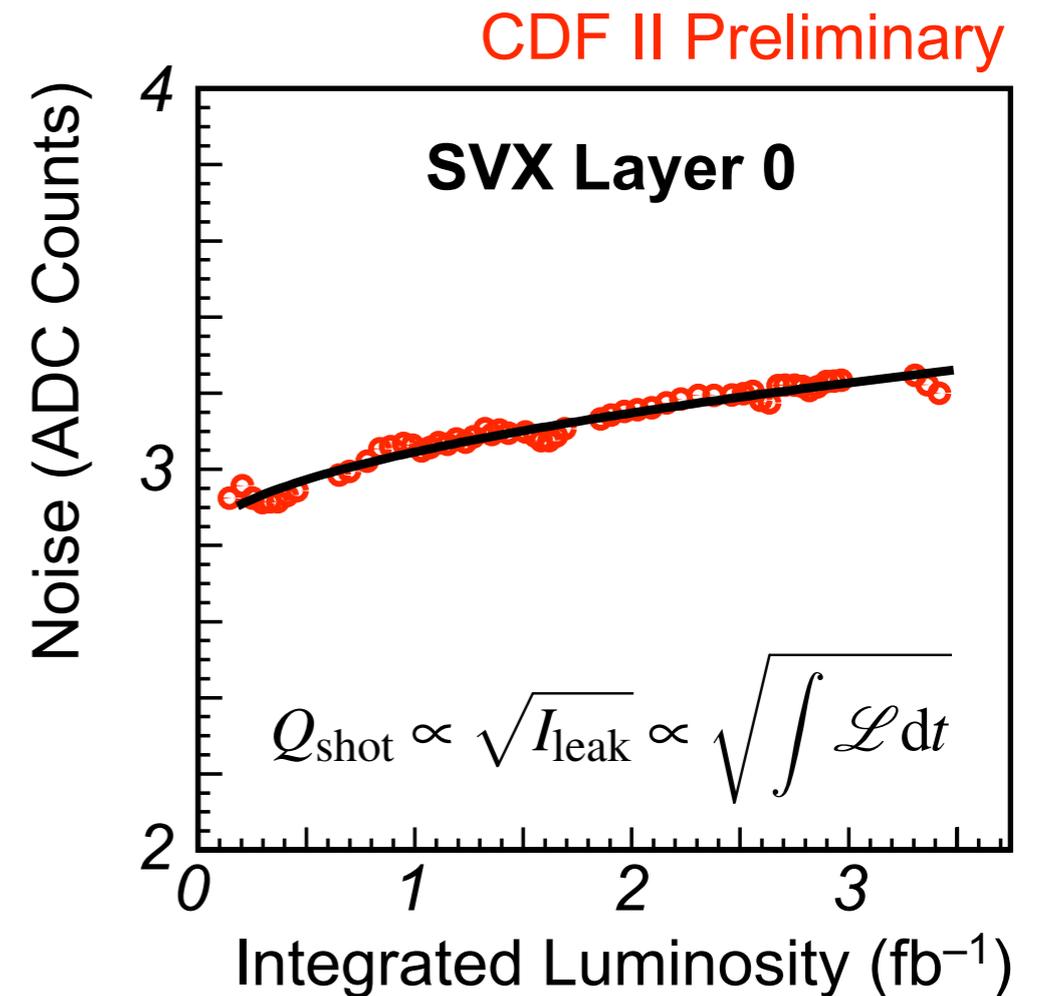
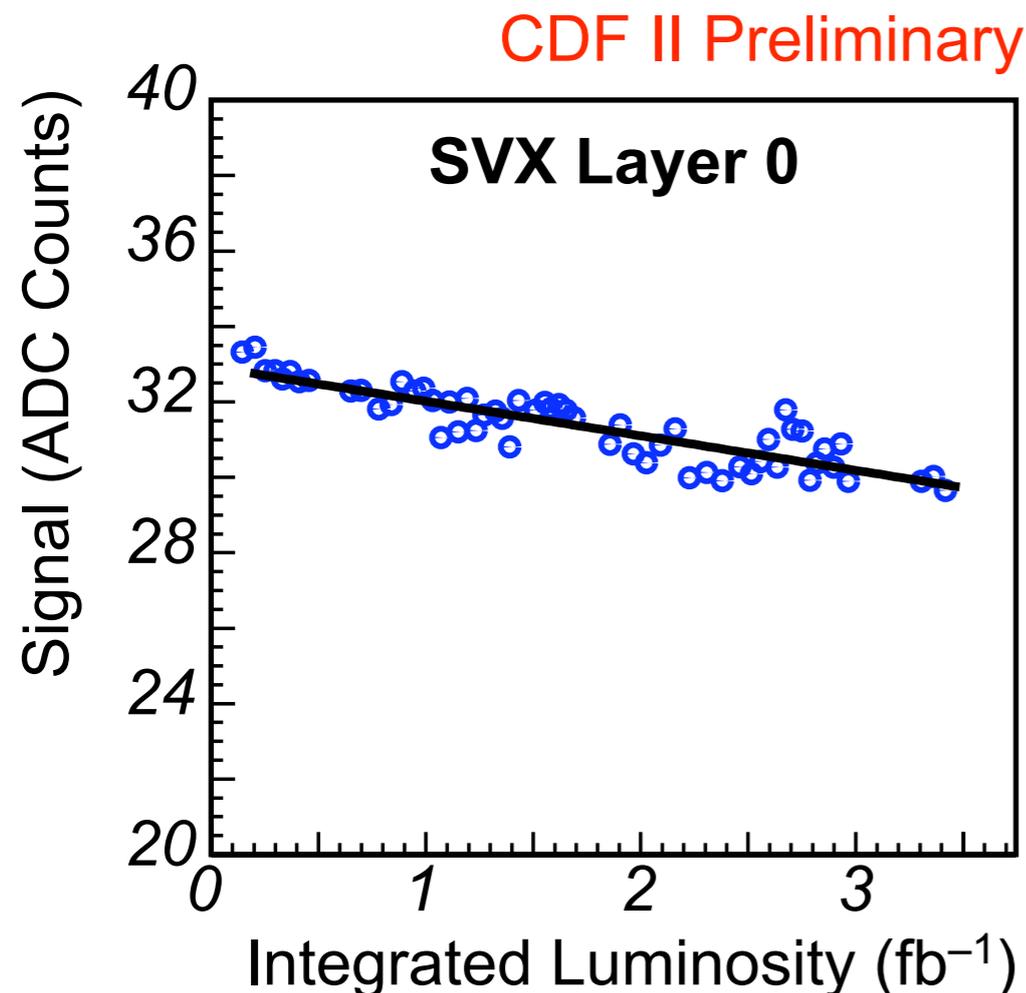


- Dataset:** full 3.1 fb⁻¹ (164 pb⁻¹ from commissioning period excluded)

- Signal:** path-length corrected charge sum of clusters using hits on tracks (J/ψ data)

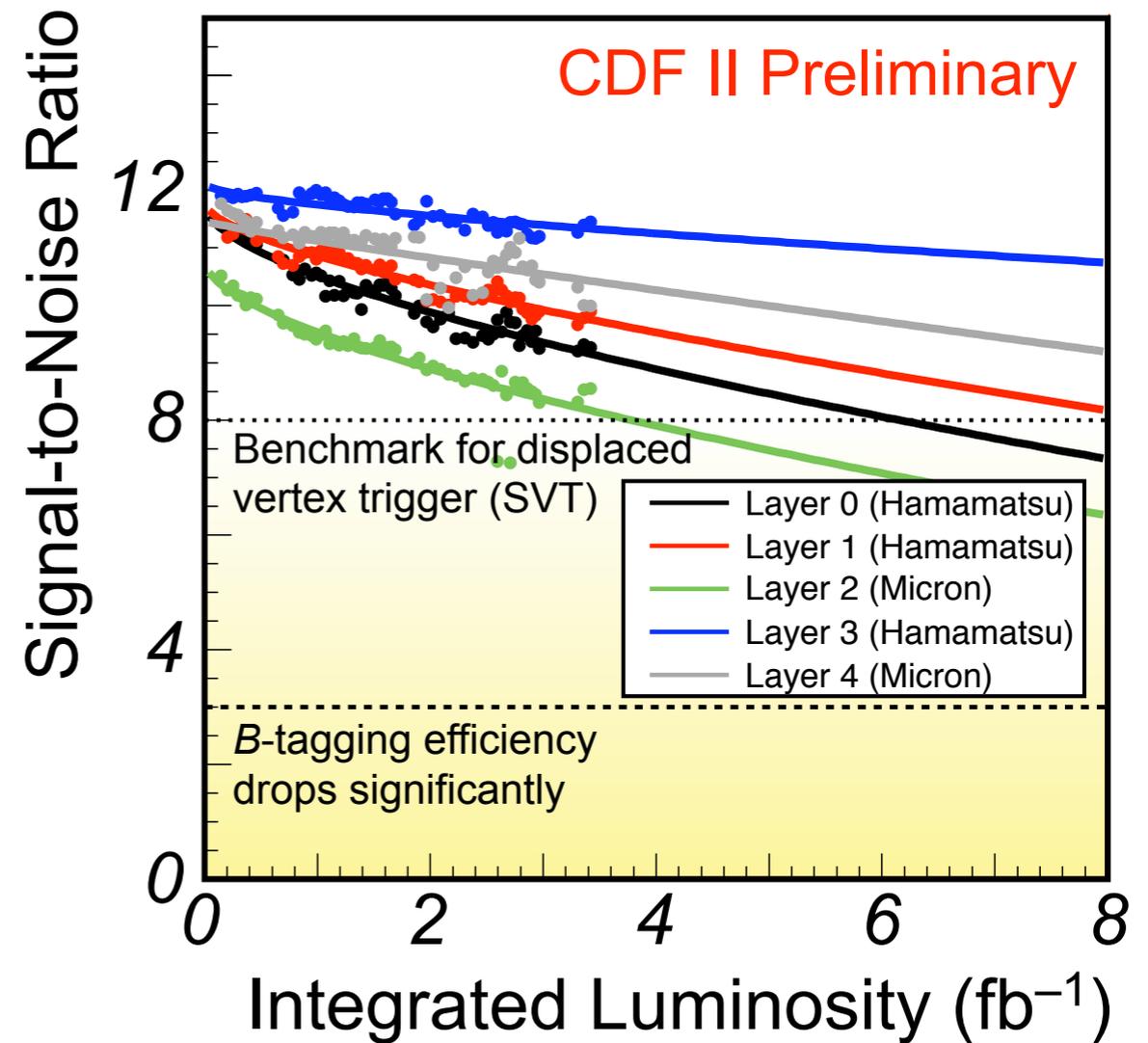
- Noise:** single-channel noise (calibration data)

- **Signal definition: most probably value of fit to ADC spectrum** (Landau distribution convoluted with Gaussian)
- Data suggest **linear decrease** with luminosity



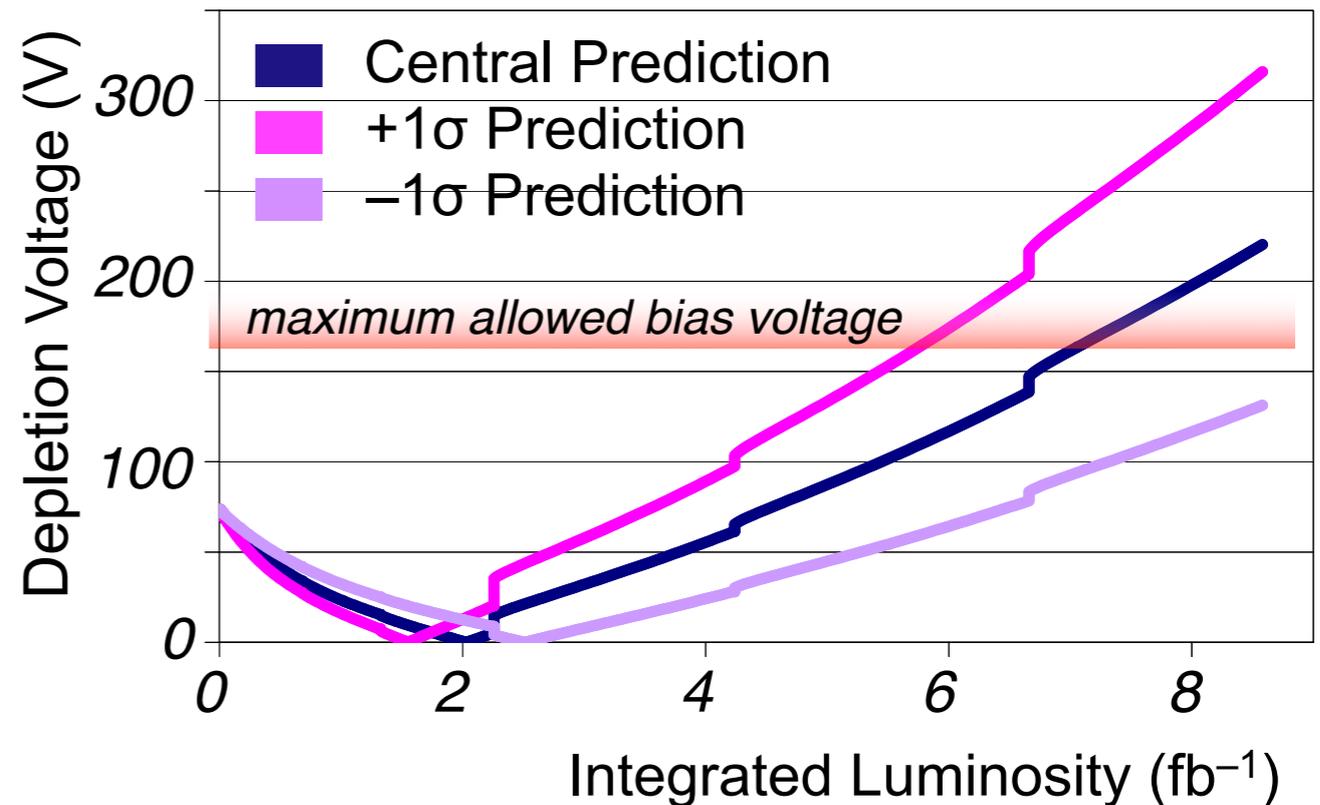
- **Noise definition: mean strip noise** obtained from calibration runs (taken every two weeks)
- Assumption: shot noise dominant source of noise: **square-root increase** with luminosity

- Fit with signal & noise model and extrapolation
 - Limit I: $SNR = 8$
(SVT efficiency drops by 5% for $SNR = 6$)
 - Limit II: $SNR = 6-3$
(b -tagging efficiency degraded)
- Conclusions:
 - SVX Layers 1, 3, 4 most probably not limited by SNR degradation
 - Need careful monitoring of Layer 0 and Layer 2



- **Due to radiation damage: evolution** of voltage needed to fully deplete sensor
- Effective number of charge carriers N_{eff} reduced until **type inversion**: decreasing depletion voltage
- Increasing depletion voltage after type inversion, eventually reaching maximum allowed bias voltage

Depletion Voltage Evolution in SVX II Layer 0



S. Worm, *Lifetime of the CDF Run II Silicon*, VERTEX 2003

Predictions: modified Hamburg model: $\Delta V_{\text{dep}} \propto \Delta N_{\text{eff}} = N_A + N_C + N_Y$

$$N_A = \Phi \sum_i g_{0,i} \exp[-c_{A,i}(T)t]$$

Beneficial Annealing

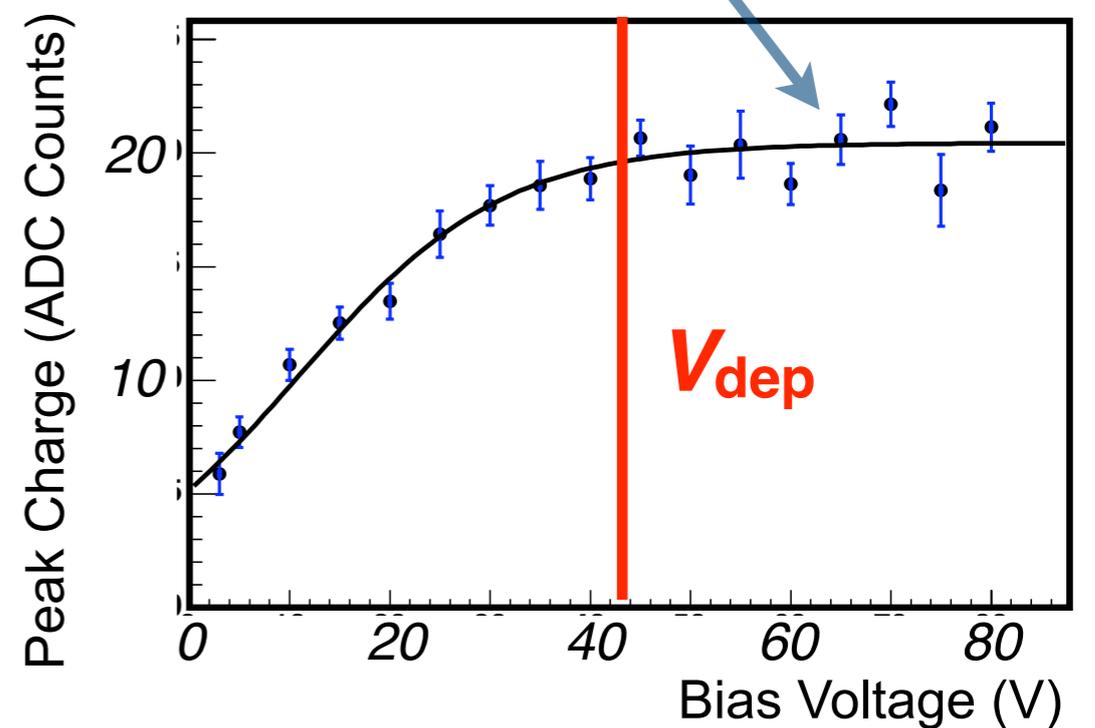
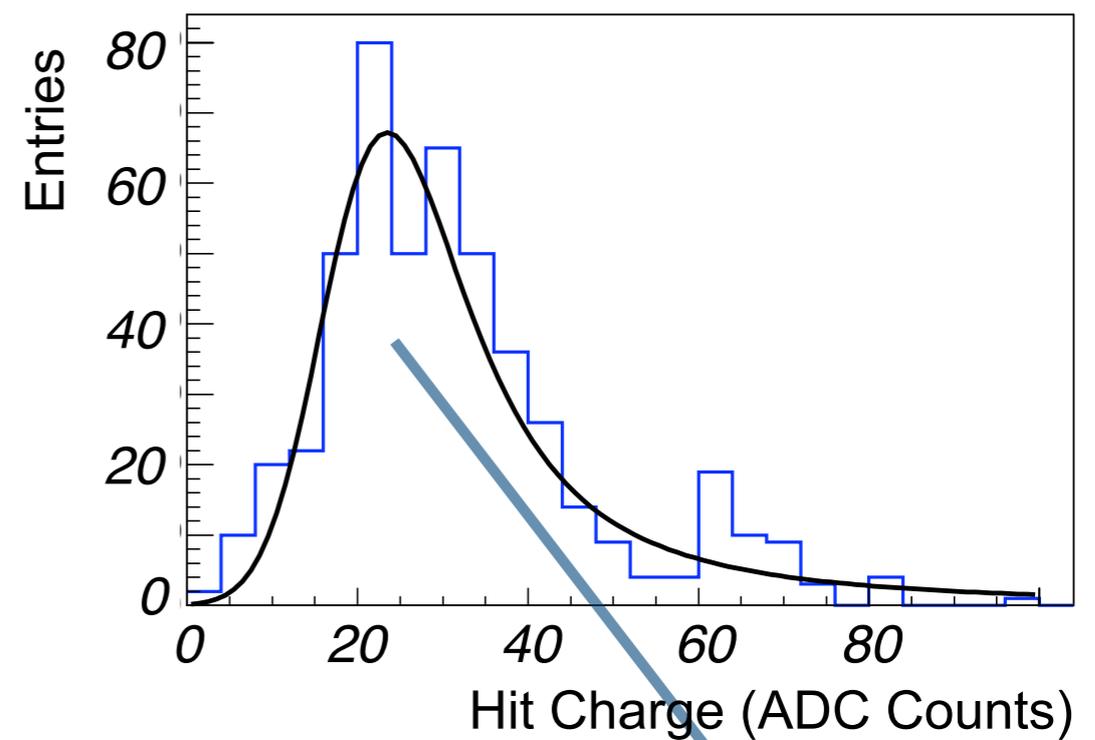
$$N_C = N_{C,0} (1 - \exp[-c\Phi]) + g_c \Phi$$

Stable Component

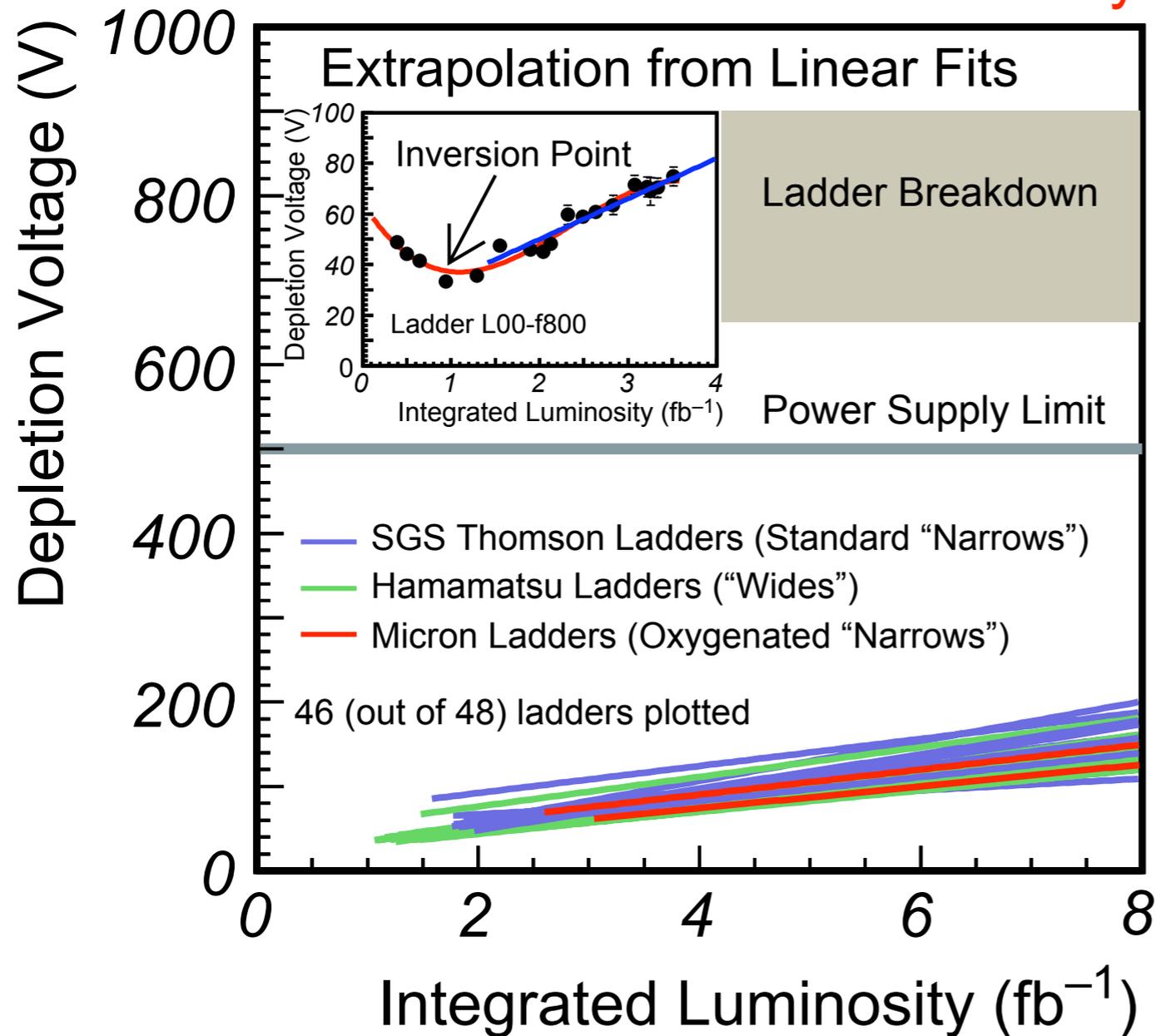
$$N_Y = g_Y \Phi \left(1 - \frac{1}{1 + g_Y \Phi c_Y(T)t} \right)$$

Reverse Annealing

- Dedicated data-taking runs (“**Signal Bias Scans**”)
- Study collected charge of silicon hits from good tracks during colliding beams operation
- Find peak of ADC spectrum as a function of bias voltage (fit: Landau \otimes Gaussian)
- Determine V_{dep} as 95% amplitude of sigmoid fit
- Operational problem: consumes valuable beam time



CDF II Preliminary



- Layer 00: very close to the beam, but built from "radiation-hard" silicon
- Evolution of depletion voltage:
 - **Type inversion** around 1 fb^{-1} (except oxygenated sensors)
 - Minimum depletion voltage around 35 V
 - **Very consistent** increase after type inversion
- Layer 00 will **outlast CDF Run II**



Summary and Conclusions



- Silicon detectors in CDF: SVX II, ISL, and L00
 - **Large and complex system**: 6 m² of sensors, 722k channels
 - **Essential** for CDF's physics program
 - **Stable performance** after long commissioning period
- LHC detectors have **profited** (and will further profit) from **Tevatron experience**, especially for Silicon detectors
- The CDF Silicon group is very active:
 - Detector maintenance and day-to-day operations: **large effort!**
 - Fixing unexpected operational issues (e.g. ISL cooling leak)
 - Detailed studies of **performance** and **longevity**
- Tevatron runs until 2009 (or 2010):
CDF will **go for the Higgs**, and the Silicon is **ready to go!**

Let's go for the Higgs! The CDF Silicon is Ready!



[CDF Silicon Workshop 2006, Santa Barbara]